



M58LW128A M58LW128B

128 Mbit (8Mb x16 or 4Mb x32, Uniform Block, Burst)
3V Supply Flash Memories

PRELIMINARY DATA

FEATURES SUMMARY

- WIDE DATA BUS for HIGH BANDWIDTH
 - M58LW128A: x16
 - M58LW128B: x16/x32
- SUPPLY VOLTAGE
 - $V_{DD} = 2.7$ to $3.6V$ core supply voltage for Program, Erase and Read operations
 - $V_{DDQ} = 1.8$ to V_{DD} for I/O Buffers
- SYNCHRONOUS/ASYNCHRONOUS READ
 - Synchronous Burst read
 - Pipelined Synchronous Burst Read
 - Asynchronous Random Read
 - Asynchronous Address Latch Controlled Read
 - Page Read
- ACCESS TIME
 - Synchronous Burst Read up to 66MHz
 - Asynchronous Page Mode Read 150/25ns
 - Random Read 150ns
- PROGRAMMING TIME
 - 16 Word or 8 Double-Word Write Buffer
 - 12 μ s Word effective programming time
- 128 UNIFORM 64 KWord MEMORY BLOCKS
- BLOCK PROTECTION/ UNPROTECTION
- PROGRAM and ERASE SUSPEND
- OTP SECURITY AREA
- COMMON FLASH INTERFACE
- 100,000 PROGRAM/ERASE CYCLES per BLOCK
- ELECTRONIC SIGNATURE
 - Manufacturer Code: 0020h
 - Device Code M58LW128A: 8818h
 - Device Code M58LW128B: 8819h

Figure 1. Packages

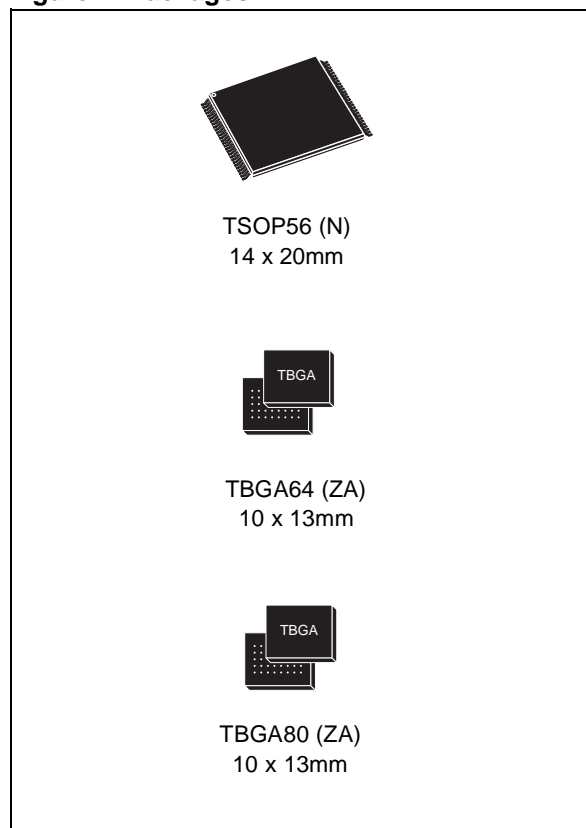


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SUMMARY DESCRIPTION

M58LW128 is a 128 Mbit (8Mb x16 or 4Mb x32) non-volatile memory that can be read, erased and reprogrammed. These operations can be performed using a single low voltage (2.7V to 3.6V) core supply. On power-up the memory defaults to Read mode with an asynchronous bus where it can be read in the same way as a non-burst Flash memory.

The memory is divided into 128 blocks of 1Mbit that can be erased independently so it is possible to preserve valid data while old data is erased. Program and Erase commands are written to the Command Interface of the memory. An on-chip Program/Erase Controller simplifies the process of programming or erasing the memory by taking care of all of the special operations that are required to update the memory contents. The end of a Program or Erase operation can be detected and any error conditions identified in the Status Register. The command set required to control the memory is consistent with JEDEC standards.

The Write Buffer allows the microprocessor to program up to 16 Words (or 8 Double Words) in parallel, both speeding up the programming and freeing up the microprocessor to perform other work. The minimum buffer size for a program operation is an 8 Word (or 4 Double Word) page. A page can only be programmed once between Erase operations.

Erase can be suspended in order to perform either read or program in any other block and then resumed. Program can be suspended to read data in any other block and then resumed. Each block can be programmed and erased over 100,000 cycles. Individual block protection against program or erase is provided for data security. All blocks are protected during power-up. The protection of the blocks is non-volatile; after power-up the protec-

tion status of each block is restored to the state when power was last removed. Software commands are provided to allow protection of some or all of the blocks and to cancel all block protection bits simultaneously. All program or erase operations are blocked when the Program Erase Enable input Vpp is low.

The Reset/Power-Down pin is used to apply a Hardware Reset to the memory and to set the device in Power-Down mode. It can also be used to temporarily disable the protection mechanism.

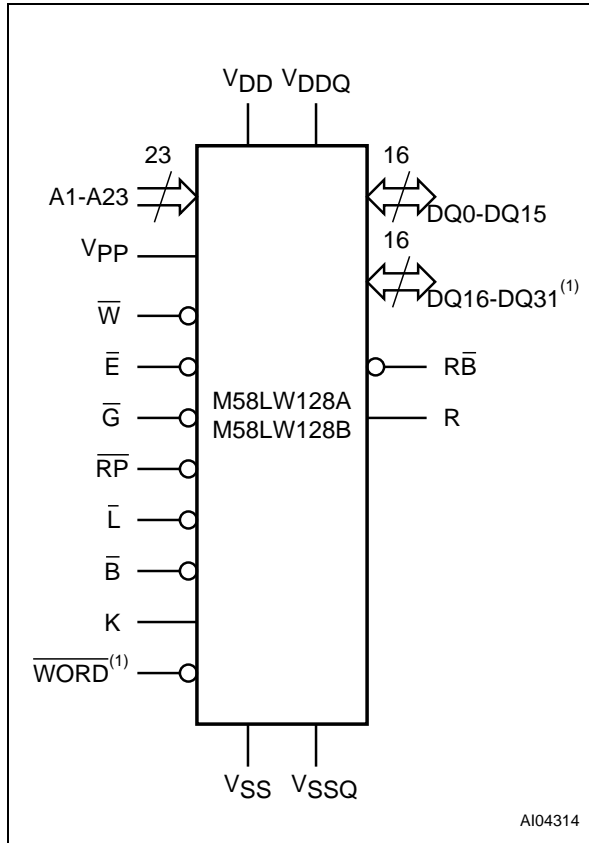
In asynchronous mode Chip Enable, Output Enable and Write Enable signals control the bus operation of the memory. An Address Latch input can be used to latch addresses in Latch Controlled mode. Together they allow simple, yet powerful, connection to most microprocessors, often without additional logic.

In synchronous mode all Bus Read operations are synchronous with the Clock. Chip Enable and Output Enable select the Bus Read operation; the address is Latched using the Latch Enable inputs and the address is advanced using Burst Address Advance. The signals are compatible with most microprocessor burst interfaces.

A One Time Programmable (OTP) area is included for security purposes. Either 512 Words (x16 Bus Width) or 512 Double-Words (x32 Bus Width) is available in the OTP area. The process of reading from and writing to the OTP area is not published for security purposes; contact STMicroelectronics for details on how to use the OTP area.

The memory is offered in various packages. The M58LW128A is available in TSOP56 (14 x 20 mm) and TBGA64 (1mm pitch). The M58LW128B is available in TBGA80 (1mm pitch).

Figure 2. Logic Diagram



Note: 1. M58LW128B only.

Table 1. Signal Names

| | |
|-------------------|---|
| A1 | Address Input (x16 Bus Width only) |
| A2-A23 | Address inputs |
| DQ0-DQ15 | Data Inputs/Outputs |
| DQ16-DQ31 | Data Inputs/Outputs (x32 Bus Width of M58LW128B only) |
| \bar{B} | Burst Address Advance |
| \bar{E} | Chip Enable |
| \bar{G} | Output Enable |
| K | Clock |
| \bar{L} | Latch Enable |
| R | Valid Data Ready |
| \bar{RB} | Ready/Busy |
| \bar{RP} | Reset/Power-Down |
| VPP | Program/Erase Enable |
| \bar{W} | Write Enable |
| \overline{WORD} | Word Organization (M58LW128B only) |
| VDD | Supply Voltage |
| VDDQ | Input/Output Supply Voltage |
| VSS | Ground |
| VSSQ | Input/Output Ground |
| NC | Not Connected Internally |

Figure 3. TSOP56 Connections

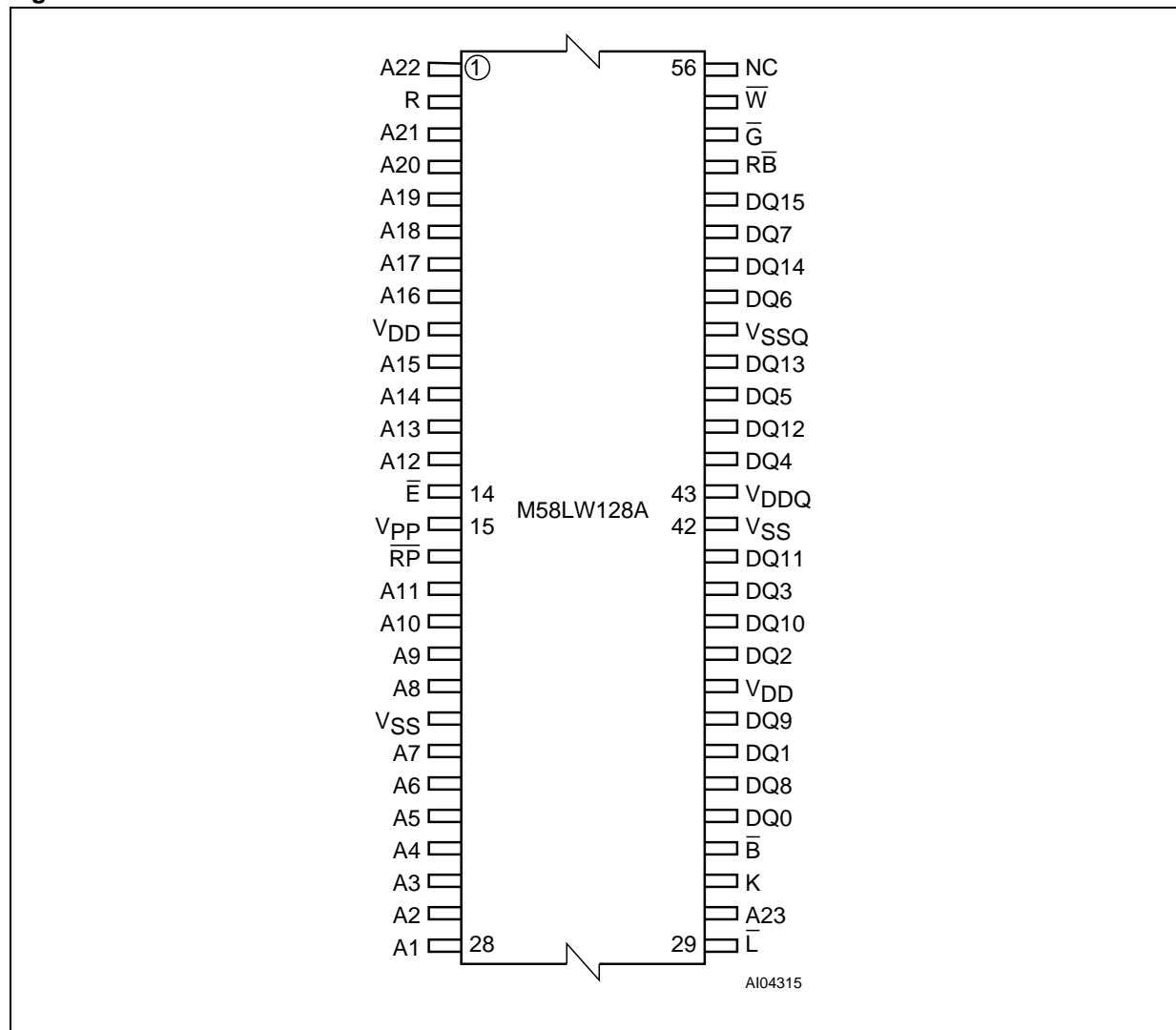
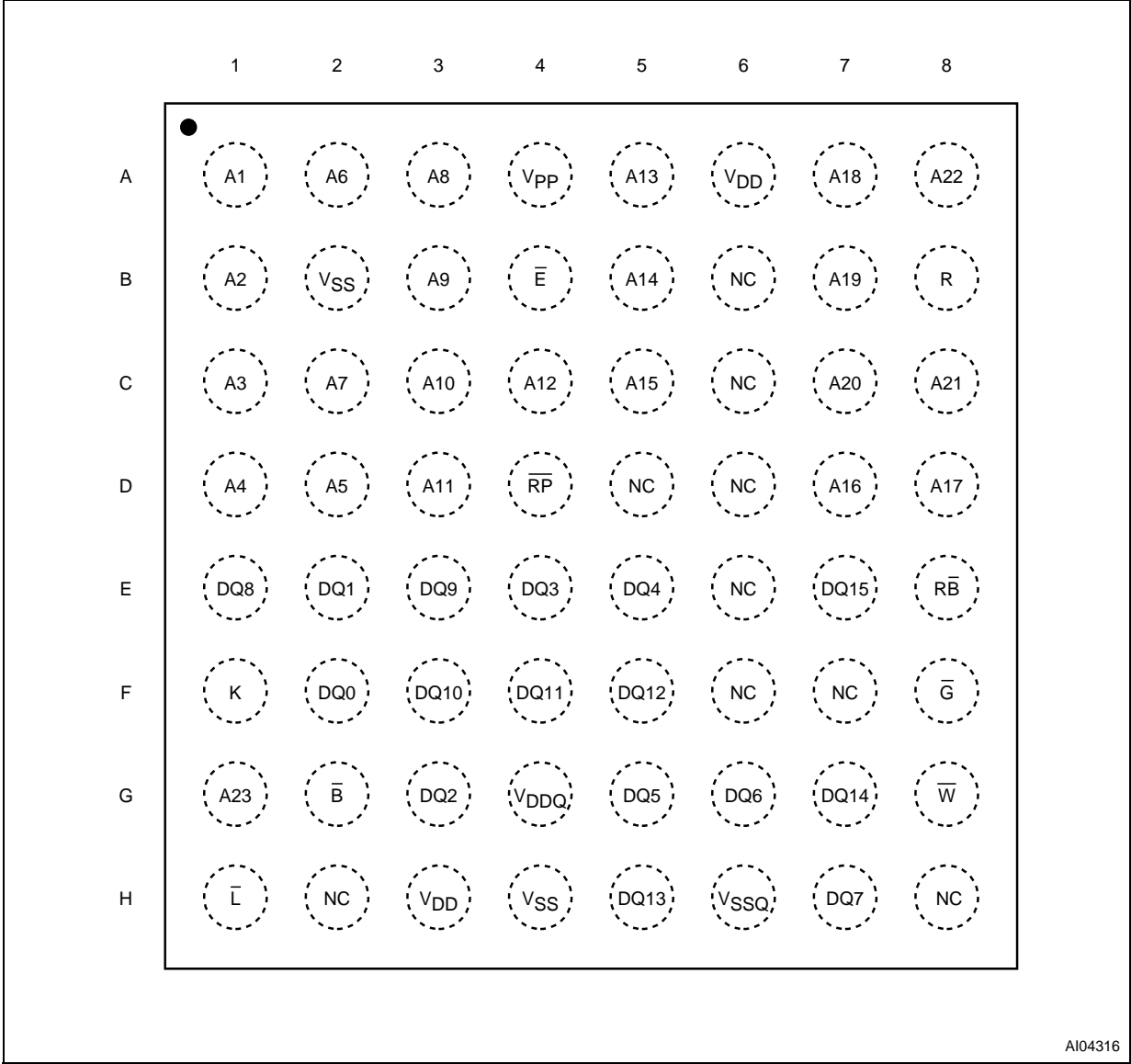
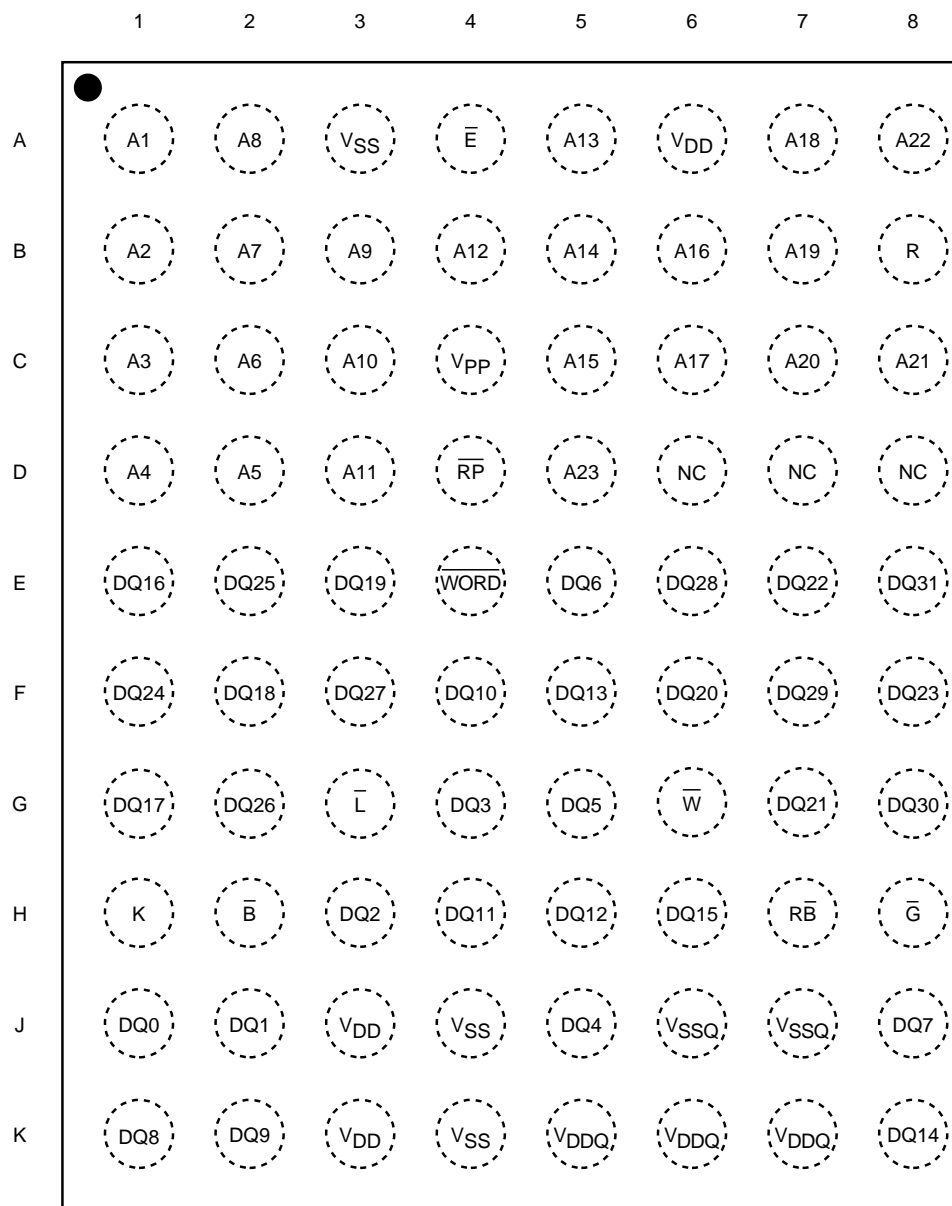


Figure 4. TBGA64 Connections for M58LW128A (Top view through package)



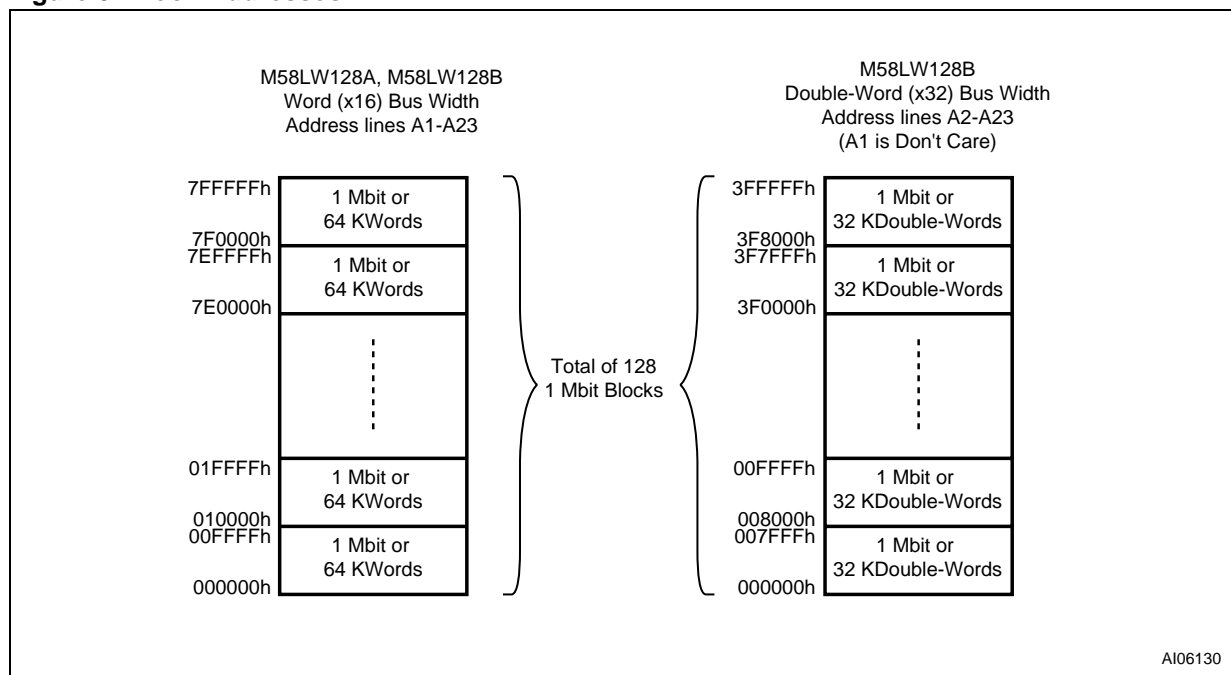
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Figure 5. TBGA80 Connections for M58LW128B (Top view through package)



AI04318

Figure 6. Block Addresses



Note: Also see Appendix A, Table 28 for a full listing of the Block Addresses

SIGNAL DESCRIPTIONS

See Figure 2, Logic Diagram and Table 1, Signal Names, for a brief overview of the signals connected to this device.

Address Inputs (A1-A23). The Address Inputs are used to select the cells to access in the memory array during Bus Read operations either to read or to program data to. During Bus Write operations they control the commands sent to the Command Interface of the internal state machine. Chip Enable must be low when selecting the addresses.

The address inputs are latched on the rising edge of Chip Enable, Write Enable or Latch Enable, whichever occurs first in a write operation. The address latch is transparent when Latch Enable is low, V_{IL} . The address is internally latched in a program or erase operation.

With a x32 Bus Width, $\overline{WORD} = V_{IH}$, Address Input A1 is ignored; the Least Significant Word is output on DQ0-DQ15 and the Most Significant Word is output on DQ16-DQ31. With a x16 Bus Width, $\overline{WORD} = V_{IL}$, the Least Significant Word is output on DQ0-DQ15 when A1 is low, V_{IL} , and the Most Significant Word is output on DQ0-DQ15 when A1 is high, V_{IH} .

Data Inputs/Outputs (DQ0-DQ31). The Data Inputs/Outputs output the data stored at the selected address during a Bus Read operation, or are used

to input the data during a Program operation. During Bus Write operations they represent the commands sent to the Command Interface of the internal state machine. When used to input data or write commands they are latched on the rising edge of Write Enable or Chip Enable, whichever occurs first.

When Chip Enable and Output Enable are both low, V_{IL} , the data bus outputs data from the memory array, the Electronic Signature, the Block Protection status, the CFI Information or the contents of the Status Register. The data bus is high impedance when the chip is deselected, Output Enable is High, V_{IH} , or the Reset/Power-Down signal is Low, V_{IL} . When the Program/Erase Controller is active the Ready/Busy status is given on DQ7 while DQ0-DQ6 and DQ8-DQ31 are high impedance.

With a x16 Bus Width, $\overline{WORD} = V_{IL}$, DQ16-DQ31 are not used and are high impedance.

Chip Enable (\overline{E}). The Chip Enable, \overline{E} , input activates the memory control logic, input buffers, decoders and sense amplifiers. Chip Enable, \overline{E} , at V_{IH} deselected the memory and reduces the power consumption to the Standby level, I_{DD1} .

Output Enable (\overline{G}). The Output Enable, \overline{G} , gates the outputs through the data output buffers during a read operation. When Output Enable, \overline{G} , is at V_{IH}

the outputs are high impedance. Output Enable, \overline{G} , can be used to inhibit the data output during a burst read operation.

Write Enable (\overline{W}). The Write Enable input, \overline{W} , controls writing to the Command Interface, Input Address and Data latches. Both addresses and data can be latched on the rising edge of Write Enable (also see Latch Enable, \overline{L}).

Reset/Power-Down (\overline{RP}). The Reset/Power-Down pin can be used to apply a Hardware Reset to the memory or to temporarily unprotect all blocks that have been protected.

A Hardware Reset is achieved by holding Reset/Power-Down Low, V_{IL} , for at least t_{PLPH} . When Reset/Power-Down is Low, V_{IL} , the Status Register information is cleared and the current is reduced to I_{DD2} (refer to Table 16, DC Characteristics). The device is deselected and outputs are high impedance. If Reset/Power-Down goes low, V_{IL} , during a Block Erase, a Write to Buffer and Program or a Block Protect/Unprotect the operation is aborted and the data may be corrupted. In this case the Ready/Busy pin stays low, V_{IL} , for a maximum timing of $t_{PLPH} + t_{PHRH}$.

After Reset/Power-Down goes High, V_{IH} , the memory will be ready for Bus Read and Bus Write operations after t_{RHEL} . Note that Ready/Busy does not fall during a reset, see Ready/Busy Output section.

During power-up Reset/Power-Down must be held Low, V_{IL} . Furthermore it must stay low for t_{VDHPH} after the Supply Voltage inputs become stable. The device will then be configured in Asynchronous Random Read mode.

See Table 23 and Figure 21, Reset, Power-Down and Power-up Characteristics, for more details.

Holding \overline{RP} at V_{HH} will temporarily unprotect the protected blocks in the memory. Program and Erase operations on all blocks will be possible.

In an application, it is recommended to associate Reset/Power-Down pin, \overline{RP} , with the reset signal of the microprocessor. Otherwise, if a reset operation occurs while the memory is performing a program or erase operation, the memory may output the Status Register information instead of being initialized to the default Asynchronous Random Read.

Latch Enable (\overline{L}). The Bus Interface can be configured to latch the Address Inputs on the rising edge of Latch Enable, \overline{L} . In synchronous bus operations the address is latched on the active edge of the Clock when Latch Enable is Low, V_{IL} . Once latched, the addresses may change without affecting the address used by the memory. When Latch Enable is Low, V_{IL} , the latch is transparent.

Clock (K). The Clock, K, is used to synchronize the memory with the external bus during Synchrono-

nous Bus Read operations. The Clock can be configured to have an active rising or falling edge. Bus signals are latched on the active edge of the Clock during synchronous bus operations. In Synchronous Burst Read mode the address is latched on the first active clock edge when Latch Enable is low, V_{IL} , or on the rising edge of Latch Enable, whichever occurs first.

During Asynchronous Bus operations the Clock is not used.

Burst Address Advance (\overline{B}). The Burst Address Advance, \overline{B} , controls the advancing of the address by the internal address counter during synchronous bus operations.

Burst Address Advance, \overline{B} , is only sampled on the active clock edge of the Clock when the X- or Y-latency time has expired. If Burst Address Advance is Low, V_{IL} , the internal address counter advances. If Burst Address Advance is High, V_{IH} , the internal address counter does not change; the same data remains on the Data Inputs/Outputs and Burst Address Advance is not sampled until the Y-latency expires.

The Burst Address Advance, \overline{B} , may be tied to V_{IL} .

Valid Data Ready (R). The Valid Data Ready output, R, is an open drain output that can be used to identify if the memory is ready to output data or not. The Valid Data Ready output is only active during Synchronous Burst Read operations when the Burst Length is set to Continuous. The Valid Data Ready output can be configured to be active on the clock edge of the invalid data read cycle or one cycle before. Valid Data Ready Low, V_{OL} , indicates that the data is not, or will not be valid. Valid Data Ready in a high-impedance state indicates that valid data is or will be available.

Unless the Burst Length is set to Continuous and Synchronous Burst Read has been selected, Valid Data Ready is high-impedance. It may be tied to other components with the same Valid Data Ready signal to create a unique System Ready signal.

When the system clock frequency is between 33MHz and 50MHz and the Y latency is set to 2, values of \overline{B} sampled on odd clock cycles, starting from the first read are not considered.

Designers should use an external pull-up resistor of the correct value to meet the external timing requirements for Valid Data Ready rising. Refer to Figure 20.

Word Organization (\overline{WORD}). The Word Organization input, \overline{WORD} , selects the x16 or x32 Bus Width on the M58LW128B. The Word Organization input is not available on the M58LW128A.

When \overline{WORD} is Low, V_{IL} , Word-wide x16 Bus Width is selected; data is read and written to DQ0-DQ15; DQ16-DQ31 are at high impedance and A1

is the LSB of the address bus. When $\overline{\text{WORD}}$ is High, V_{IH} , the Double-Word wide x32 Bus Width is selected and the data is read and written to on DQ0-DQ31; A2 is the LSB of the address bus and A1 is don't care.

Ready/Busy ($\overline{\text{RB}}$). The Ready/Busy output, $\overline{\text{RB}}$, is an open-drain output that can be used to identify if the Program/Erase Controller is currently active. When Ready/Busy is high impedance, the memory is ready for any read, program or erase operation. Ready/Busy is Low, V_{OL} , during program and erase operations. When the device is busy it will not accept any additional Program or Erase commands except Program/Erase Suspend. When the Program/Erase Controller is idle, or suspended, Ready/Busy can float High through a pull-up resistor.

The use of an open-drain output allows the Ready/Busy pins from several memories to be connected to a single pull-up resistor. A Low will then indicate that one, or more, of the memories is busy.

Ready/Busy is not Low during a reset unless the reset was applied when the Program/Erase Controller was active; Ready/Busy can rise before Reset/Power-Down rises.

Program/Erase Enable (V_{PP}). The Program/Erase Enable input, V_{PP} , is used to protect all blocks, preventing Program and Erase operations from affecting their data.

When Program/Erase Enable is Low, V_{IL} , any program or erase operation sent to the Command Interface will cause the V_{PP} Status bit (bit3) in the Status Register to be set. When Program/Erase Enable is High, V_{IH} , program and erase operations can be performed on unprotected blocks. Program/Erase Enable must be kept High during all Program, Erase, Block Protect and Block Unpro-

tect operations, otherwise the operation is not guaranteed to succeed and data may become corrupt.

V_{DD} Supply Voltage. The Supply Voltage, V_{DD} , is the core power supply. All internal circuits draw their current from the V_{DD} pin, including the Program/Erase Controller.

A 0.1 μF capacitor should be connected between the Supply Voltage, V_{DD} , and the Ground, V_{SS} , to decouple the current surges from the power supply. The PCB track widths must be sufficient to carry the currents required during all operations of the parts, see Table 16, DC Characteristics, for maximum current supply requirements.

Input/Output Supply Voltage (V_{DDQ}). The Input/Output Supply Voltage, V_{DDQ} , is the input/output buffer power supply. All input and output pins and voltage references are powered and measured relative to the Input/Output Supply Voltage pin, V_{DDQ} .

The Input/Output Supply Voltage, V_{DDQ} , must always be equal or less than the V_{DD} Supply Voltage, including during Power-Up.

A 0.1 μF capacitor should be connected between the Input/Output Supply Voltage, V_{DDQ} , and the Ground, V_{SSQ} , to decouple the current surges from the power supply. If V_{DDQ} and V_{DD} are connected together then only one decoupling capacitor is required.

Ground (V_{SS}). Ground, V_{SS} , is the reference for all core power supply voltages.

Ground (V_{SSQ}). Ground, V_{SSQ} , is the reference for input/output voltage measurements. It is essential to connect V_{SS} and V_{SSQ} to the same ground.

BUS OPERATIONS

The bus operations that control the memory are described in this section, see Tables 2 and 3, Bus Operations, for a summary. The bus operation is selected through the Burst Configuration Register; the bits in this register are described at the end of this section.

On Power-up or after a Hardware Reset the memory defaults to Asynchronous Bus Read and Asynchronous Bus Write, no other bus operation can be performed until the Burst Control Register has been configured.

Synchronous Read operations and Latch Controlled Bus Read operations can only be used to read the memory array. The Electronic Signature, CFI or Status Register will be read in asynchronous mode regardless of the Burst Control Register settings.

Typically glitches of less than 5ns on Chip Enable or Write Enable are ignored by the memory and do not affect bus operations.

Asynchronous Bus Operations

For asynchronous bus operations refer to Table 3 together with the text below.

Asynchronous Bus Read. Asynchronous Bus Read operations read from the memory cells, or specific registers (Electronic Signature, Status Register, CFI and Block Protection Status) in the Command Interface. A valid bus operation involves setting the desired address on the Address Inputs, applying a Low signal, V_{IL} , to Chip Enable and Output Enable and keeping Write Enable High, V_{IH} . The Data Inputs/Outputs will output the value, see Figure 12, Asynchronous Bus Read AC Waveforms, and Table 17, Asynchronous Bus Read AC Characteristics, for details of when the output becomes valid.

Asynchronous Latch Controlled Bus Read.

Asynchronous Latch Controlled Bus Read operations read from the memory cells. The address is latched in the memory before the value is output on the data bus, allowing the address to change during the cycle without affecting the address that the memory uses.

A valid bus operation involves setting the desired address on the Address Inputs, setting Chip Enable and Address Latch Low, V_{IL} and keeping Write Enable High, V_{IH} ; the address is latched on the rising edge of Address Latch. Once latched, the Address Inputs can change. Set Output Enable Low, V_{IL} , to read the data on the Data Inputs/Outputs; see Figure 13, Asynchronous Latch Controlled Bus Read AC Waveforms and Table 18, Asynchronous Latch Controlled Bus Read AC Characteristics for details on when the output becomes valid.

Note that, since the Latch Enable input is transparent when set Low, V_{IL} , Asynchronous Bus Read operations can be performed when the memory is configured for Asynchronous Latch Enable bus operations by holding Latch Enable Low, V_{IL} throughout the bus operation.

Asynchronous Page Read. Asynchronous Page Read operations are used to read from several addresses within the same memory page. Each memory page is 8 Words or 4 Double-Words and has the same A4-A23, only A1, A2 and A3 may change.

Valid bus operations are the same as Asynchronous Bus Read operations but with different timings. The first read operation within the page has identical timings, subsequent reads within the same page have much shorter access times. If the page changes then the normal, longer timings apply again. See Figure 14, Asynchronous Page Read AC Waveforms and Table 19, Asynchronous Page Read AC Characteristics for details on when the outputs become valid.

Asynchronous Bus Write. Asynchronous Bus Write operations write to the Command Interface in order to send commands to the memory or to latch addresses and input data to program. Bus Write operations are asynchronous, the clock, K, is don't care during Bus Write operations.

A valid Asynchronous Bus Write operation begins by setting the desired address on the Address Inputs and setting Latch Enable Low, V_{IL} . The Address Inputs are latched by the Command Interface on the rising edge of Chip Enable or Write Enable, whichever occurs first. The Data Inputs/Outputs are latched by the Command Interface on the rising edge of Chip Enable or Write Enable, whichever occurs first. Output Enable must remain High, V_{IH} , during the whole Asynchronous Bus Write operation. See Figures 15, and 17, Asynchronous Write AC Waveforms, and Tables 20 and 21, Asynchronous Write and Latch Controlled Write AC Characteristics, for details of the timing requirements.

Asynchronous Latch Controlled Bus Write.

Asynchronous Latch Controlled Bus Write operations write to the Command Interface in order to send commands to the memory or to latch addresses and input data to program. Bus Write operations are asynchronous, the clock, K, is don't care during Bus Write operations.

A valid Asynchronous Latch Controlled Bus Write operation begins by setting the desired address on the Address Inputs and pulsing Latch Enable Low, V_{IL} . The Address Inputs are latched by the Command Interface on the rising edge of Latch Enable, Chip Enable or Write Enable, whichever occurs

first. The Data Inputs/Outputs are latched by the Command Interface on the rising edge of Chip Enable or Write Enable, whichever occurs first. Output Enable must remain High, V_{IH} , during the whole Asynchronous Bus Write operation. See Figures 16 and 18 Asynchronous Latch Controlled Write AC Waveforms, and Tables 20 and 21, Asynchronous Write and Latch Controlled Write AC Characteristics, for details of the timing requirements.

Output Disable. The Data Inputs/Outputs are in the high impedance state when the Output Enable is High.

Standby. When Chip Enable is High, V_{IH} , the memory enters Standby mode and the Data In-

puts/Outputs pins are placed in the high impedance state regardless of Output Enable or Write Enable. The Supply Current is reduced to the Standby Supply Current, I_{DD1} .

During Program or Erase operations the memory will continue to use the Program/Erase Supply Current, I_{DD3} , for Program or Erase operations until the operation completes.

Power-Down. The memory is in Power-Down mode when Reset/Power-Down, \overline{RP} , is Low. The current is reduced to I_{DD2} , and the outputs are high impedance, independent of Chip Enable, Output Enable or Write Enable.

Table 2. Asynchronous Bus Operations

| Bus Operation | Step | \overline{E} | \overline{G} | \overline{W} | \overline{RP} | M3 ⁽²⁾ | \overline{L} | A1-A23 | DQ0-DQ31 |
|---|---------------|----------------|----------------|----------------|-----------------|-------------------|----------------|---------|-------------|
| Asynchronous Bus Read | | V_{IL} | V_{IL} | V_{IH} | High | 0 | X | Address | Data Output |
| Asynchronous Latch Controlled Bus Read | Address Latch | V_{IL} | V_{IL} | V_{IH} | High | 1 | V_{IL} | Address | High Z |
| | Read | V_{IL} | V_{IL} | V_{IH} | High | 1 | V_{IH} | X | Data Output |
| Asynchronous Page Read | | V_{IL} | V_{IL} | V_{IH} | High | 0 | X | Address | Data Output |
| Asynchronous Bus Write | | V_{IL} | V_{IH} | V_{IL} | High | X | V_{IL} | Address | Data Input |
| Asynchronous Latch Controlled Bus Write | Address Latch | V_{IL} | V_{IH} | V_{IL} | High | X | V_{IL} | Address | Data Input |
| Output Disable | | V_{IL} | V_{IH} | V_{IH} | High | X | X | X | High Z |
| Standby | | V_{IH} | X | X | High | X | X | X | High Z |
| Power-Down | | X | X | X | V_{IL} | X | X | X | High Z |

Note: 1. X = Don't Care V_{IL} or V_{IH} . High = V_{IH} or V_{HH} .

2. M15 = 1, Bits M15 and M3 are in the Burst Configuration Register.

Synchronous Bus Operations

For synchronous bus operations refer to Table 3 together with the text below.

Synchronous Burst Read. Synchronous Burst Read operations are used to read from the memory at specific times synchronized to an external reference clock. The burst type, length and latency can be configured. The different configurations for Synchronous Burst Read operations are described in the Burst Configuration Register section.

A valid Synchronous Burst Read operation begins when the address is set on the Address Inputs, Write Enable is High, V_{IH} , and Chip Enable and Latch Enable are Low, V_{IL} , during the active edge of the Clock. The address is latched on the first active clock edge when Latch Enable is low, or on the rising edge of Latch Enable, whichever occurs first. The data becomes available for output after the X-latency specified in the Burst Control Register has expired. The output buffers are activated by setting Output Enable Low, V_{IL} . See Figure 7 for an example of a Synchronous Burst Read operation.

The Burst Address Advance input and the Y-latency specified in the Burst Control Register determine whether the internal address counter is advanced on the active edge of the Clock. When the internal address counter is advanced the Data Inputs/Outputs change to output the value for the next address.

In Continuous Burst mode (Burst Length Bit M2-M0 is set to '111'), one Burst Read operation can access the entire memory sequentially and wrap at the last address. The Burst Address Advance, \bar{B} , must be kept low, V_{IL} , for the appropriate number of clock cycles. If Burst Address Advance, \bar{B} , is pulled High, V_{IH} , the Burst Read will be suspended.

In Continuous Burst Mode, if the starting address is not associated with a page (4 Word or 2 Double Word) boundary the Valid Data Ready, R, output goes Low, V_{IL} , to indicate that the data will not be ready in time and additional wait-states are required. The Valid Data Ready output timing (bit M8) can be changed in the Burst Configuration Register.

When using the x32 Bus Width certain X-latencies are not valid and must not be used; see Table 5, Burst Configuration Register.

The Synchronous Burst Read timing diagrams and AC Characteristics are described in the AC and DC Parameters section. See Figures 19, 20 and Table 22.

Synchronous Pipelined Burst Read. Synchronous Burst Read operations can be overlapped to avoid or reduce the X-latency. Pipelined operations should only be used with Burst Configuration Register bit M9 = 0 (Y-latency setting).

A valid Synchronous Pipelined Burst Read operation occurs during a Synchronous Burst Read operation when the new address is set on the Address Inputs and a Low pulse is applied to Latch Enable. The data for the new address becomes valid after the X-latency specified in the Burst Configuration Register has expired.

For optimum operation the address should be latched on the correct clock cycle. Table 4 gives the clock cycle for each valid X- and Y-latency setting. Only these settings are valid, other settings must not be used. There is always one Y-Latency period where the data is not valid. If the address is latched later than the clock cycle specified in Tables 4 then additional cycles where the data is not valid are inserted. See Figure 8 for an example of a Synchronous Pipelined Burst Read operation. Here the X-latency is 8, the Y-latency is 1 and the burst length is 4; the first address is latched on cycle 1 while the next address is latched on cycle 6, as shown in Table 4.

Synchronous Pipelined Burst Read operations should only be performed on Burst Lengths of 4 or 8 with a x16 Bus Width or a Burst Length of 4 with a x32 Bus Width.

Suspending a Pipelined Synchronous Burst Read operation is not recommended.

Synchronous Burst Read Suspend. During a Synchronous Burst Read operation it is possible to suspend the operation, freeing the data bus for other higher priority devices.

A valid Synchronous Burst Read operation is suspended when both Output Enable and Burst Address Advance are High, V_{IH} . The Burst Address Advance going High, V_{IH} , stops the burst counter and the Output Enable going High, V_{IH} , inhibits the data outputs. The Synchronous Burst Read operation can be resumed by setting Output Enable Low. See Figure 7 for an example of a Synchronous Burst Read Suspend operation.

Table 3. Synchronous Burst Read Bus Operations

| Bus Operation | Step | \bar{E} | \bar{G} | \bar{RP} | $K^{(3)}$ | \bar{L} | \bar{B} | A1-A23 DQ0-DQ31 |
|----------------------------------|------------------------------------|-----------|-----------|------------|-----------|-----------|-----------|--------------------|
| Synchronous Burst Read | Address Latch | V_{IL} | X | V_{IH} | T | V_{IL} | X | Address Input |
| | Read (no address advance) | V_{IL} | V_{IL} | V_{IH} | T | X | V_{IH} | Data Output |
| | Read (with address advance) | V_{IL} | V_{IL} | V_{IH} | T | X | V_{IL} | Data Output |
| Pipelined Synchronous Burst Read | Read Suspend | V_{IL} | V_{IH} | V_{IH} | X | X | V_{IH} | High Z |
| | Read Resume (no address advance) | V_{IL} | V_{IL} | V_{IH} | T | X | V_{IH} | Data Output |
| | Read Resume (with address advance) | V_{IL} | V_{IL} | V_{IH} | T | X | V_{IL} | Data Output |
| | Read Abort | V_{IH} | X | V_{IH} | X | X | X | High Z |

Note: 1. X = Don't Care, V_{IL} or V_{IH} .

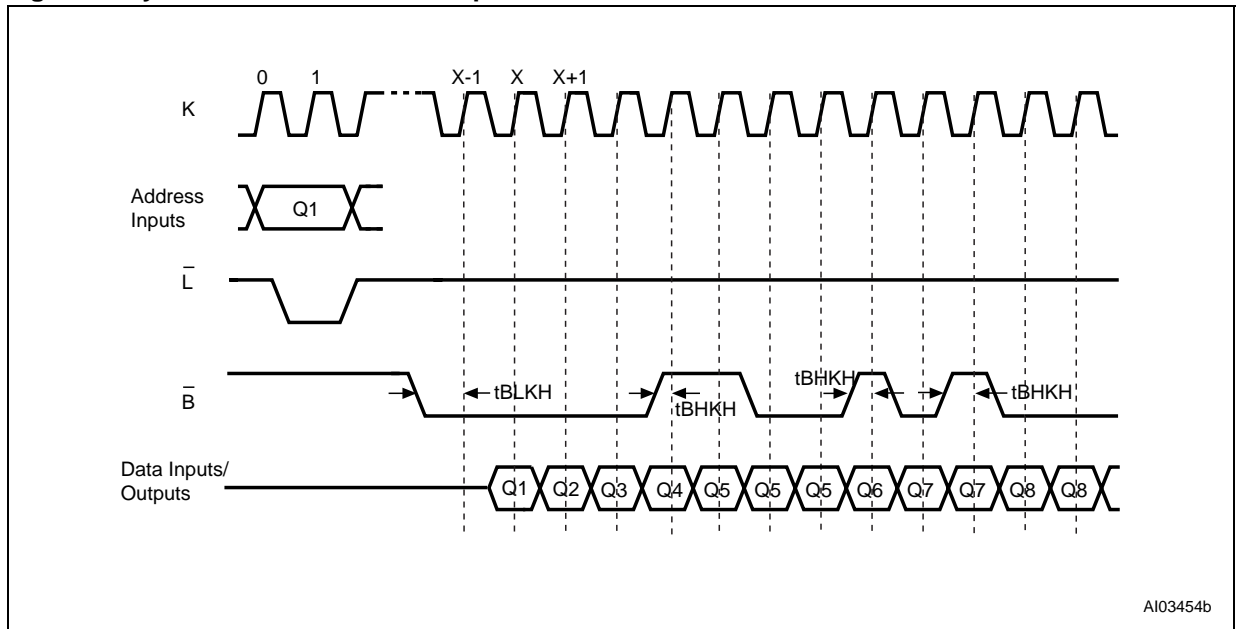
2. M15 = 0, Bit M15 is in the Burst Configuration Register.

3. T = transition, see M6 in the Burst Configuration Register for details on the active edge of K.

Table 4. Address Latch Cycle for Optimum Pipelined Synchronous Burst Read

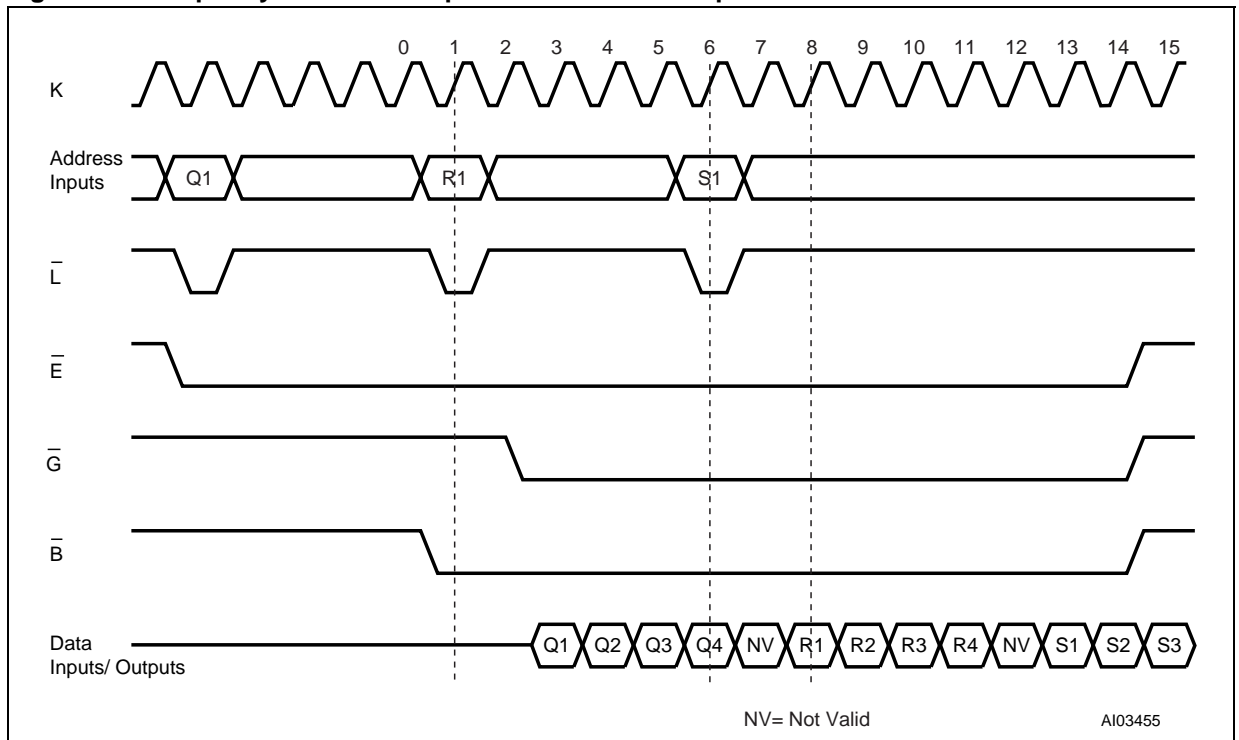
| X-Latency | Y-Latency | Address Latch Clock Cycle | |
|-----------|-----------|---------------------------|------------------|
| | | Burst Length = 4 | Burst Length = 8 |
| 8 | 1 | 6 | 10 |
| 9 | 1 | 7 | 11 |
| 12 | 1 | 10 | 14 |
| 13 | 1 | 11 | 15 |
| 15 | 2 | 11 | 19 |

Figure 7. Synchronous Burst Read Operation



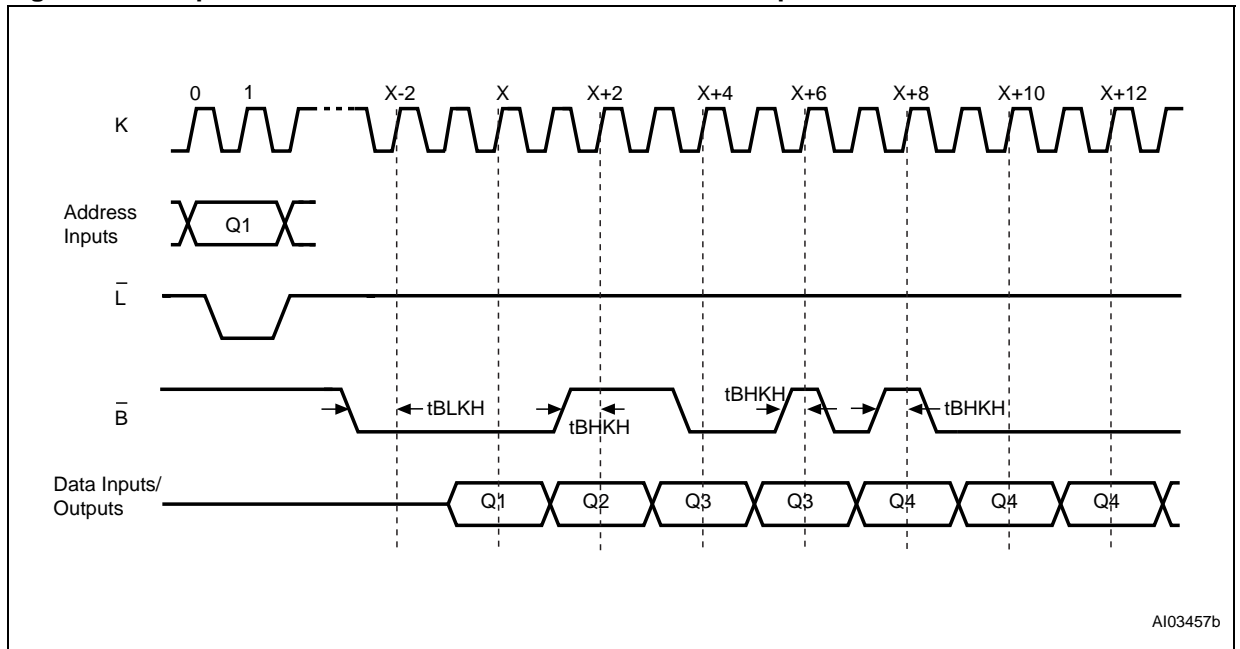
Note: In this example the Burst Configuration Register is set with M2-M0 = 001 (Burst Length = 4 Words or Double Words), M6 = 1 (Valid Clock Edge = Rising Clock Edge), M7 = 0 or 1 (Burst Type = Interleaved or Sequential), M9 = 0 (Y-Latency = 1), M14-M11 = 0011 (X-Latency = 8) and M15 = 0 (Read Select = Synchronous Burst Read), other bits are don't care.

Figure 8. Example Synchronous Pipelined Burst Read Operation



Note: In this example the Burst Configuration Register is set with M2-M0 = 001 (Burst Length = 4 Words or Double Words), M6 = 1 (Valid Clock Edge = Rising Clock Edge), M7 = 0 or 1 (Burst Type = Interleaved or Sequential), M9 = 0 (Y-Latency = 1), M14-M11 = 0011 (X-Latency = 8) and M15 = 0 (Read Select = Synchronous Burst Read), other bits are don't care.

Figure 9. Example Burst Address Advance and Burst Abort operations



AI03457b

- Note: 1. In this example the Burst Configuration Register is set with M2-M0 = 010 (Burst Length = 8 Words), M6 = 1 (Valid Clock Edge = Rising Clock Edge), M7 = 0 or 1 (Burst Type = Interleaved or Sequential), M9 = 1 (Y-Latency = 2), M14-M11 = 0011 (X-Latency = 8) and M15 = 0 (Read Select = Synchronous Burst Read), other bits are don't care.
2. When the system clock frequency is between 33MHz and 50MHz and the Y latency is set to 2, values of \bar{B} sampled on odd clock cycles, starting from the first read are not considered.

Burst Configuration Register

The Burst Configuration Register is used to configure the type of bus access that the memory will perform.

The Burst Configuration Register is set through the Command Interface and will retain its information until it is re-configured, the device is reset, or the device goes into Reset/Power-Down mode. The Burst Configuration Register bits are described in Table 5. They specify the selection of the burst length, burst type, burst X and Y latencies and the Read operation.

Read Select Bit (M15). The Read Select bit, M15, is used to switch between asynchronous and synchronous Bus Read operations. When the Read Select bit is set to '1', Bus Read operations are asynchronous; when the Read Select bit is set to '0', Bus Read operations are synchronous.

On reset or power-up the Read Select bit is set to '1' for asynchronous accesses.

X-Latency Bits (M14-M11). The X-Latency bits are used during Synchronous Bus Read operations to set the number of clock cycles between the address being latched and the first data becoming available. For correct operation the X-Latency bits can only assume the values in Table 5, Burst Configuration Register. The X-Latency bits should also be selected in conjunction with Table 8, Burst Performance to ensure valid settings.

Y-Latency Bit (M9). The Y-Latency bit is used during Synchronous Bus Read operations to set the number of clock cycles between consecutive reads. The Y-Latency value depends on both the X-Latency value and the setting in M9.

When the Y-Latency is 1 the data changes each clock cycle; when the Y-Latency is 2 the data changes every second clock cycle. See Table 5, Burst Configuration Register and Table 8, Burst Performance, for valid combinations of the Y-Latency, the X-Latency and the Clock frequency.

Valid Data Ready Bit (M8). The Valid Data Ready bit controls the timing of the Valid Data

Ready output pin, R. When the Valid Data Ready bit is '0' the Valid Data Ready output pin is driven Low for the active clock edge when invalid data is output on the bus. When the Valid Data Ready bit is '1' the Valid Data Ready output pin is driven Low one clock cycle prior to invalid data being output on the bus.

Burst Type Bit (M7). The Burst Type bit is used to configure the sequence of addresses read as sequential or interleaved. When the Burst Type bit is '0' the memory outputs from interleaved addresses; when the Burst Type bit is '1' the memory outputs from sequential addresses. See Tables 6 and 7, Burst Type Definition, for the sequence of addresses output from a given starting address in each mode.

Valid Clock Edge Bit (M6). The Valid Clock Edge bit, M6, is used to configure the active edge of the Clock, K, during Synchronous Burst Read operations. When the Valid Clock Edge bit is '0' the falling edge of the Clock is the active edge; when the Valid Clock Edge bit is '1' the rising edge of the Clock is active.

Latch Enable Bit (M3). The Latch Enable bit is used to select between Asynchronous Random Read and Asynchronous Latch Enable Controlled Read. When the Latch Enable bit is set to '0' Random read is selected; when it is set to '1' Latch Enable Controlled Read is selected. To enable these Asynchronous Read configurations M15 must be set to '1'.

Burst Length Bit (M2-M0). The Burst Length bits set the maximum number of Words or Double-Words that can be output during a Synchronous Burst Read operation before the address wraps.

Table 5, Burst Configuration Register gives the valid combinations of the Burst Length bits that the memory accepts; Tables 6 and 7, Burst Type Definition, give the sequence of addresses output from a given starting address for each length.

M10, M5 and M4 are reserved for future use.

Table 5. Burst Configuration Register

| Address Bit | Mnemonic | Bit Name | Reset Value | Value | Description | Valid Bus Width |
|-------------|----------|------------------|-------------|--------|---|-----------------|
| 17 | M15 | Read Select | 1 | 0 | Synchronous Burst Read | x16 or x32 |
| | | | | 1 | Asynchronous Bus Read | x16 or x32 |
| 16 to 13 | M14-M11 | X-Latency | XXXX | 0010 | X-Latency = 7, use only with Continuous Burst Length | x16 or x32 |
| | | | | 0011 | X-Latency = 8 | x16 or x32 |
| | | | | 0100 | X-Latency = 9 | x16 or x32 |
| | | | | 0101 | X-Latency = 10, use only with Continuous Burst Length | x16 only |
| | | | | 0110 | X-Latency = 11, use only with Continuous Burst Length | x16 only |
| | | | | 1001 | X-Latency = 12 | x16 only |
| | | | | 1010 | X-Latency = 13 | x16 only |
| | | | | 1011 | X-Latency = 13, use only with Continuous Burst Length | x16 or x32 |
| | | | | 1101 | X-Latency = 15 | x16 or x32 |
| | | | | Others | Reserved, Do Not Use. | |
| 11 | M9 | Y-Latency | X | 0 | When X-Latency < 13, Y-Latency = 1 When M14-M11 = 1011 or 1101, Y-Latency = 2 | x16 or x32 |
| | | | | 1 | When X-Latency ≤ 15 but M14-M11 ≠ 1011 or 1101, Y-Latency = 2, When M14-M11 = 1011 or 1101 DO NOT USE. | x16 or x32 |
| 10 | M8 | Valid Data Ready | X | 0 | R valid Low during valid Clock edge | x16 or x32 |
| | | | | 1 | R valid Low one cycle before valid Clock edge | x16 or x32 |
| 9 | M7 | Burst Type | X | 0 | Interleaved | x16 or x32 |
| | | | | 1 | Sequential | x16 or x32 |
| 8 | M6 | Valid Clock Edge | X | 0 | Falling Clock edge | x16 or x32 |
| | | | | 1 | Rising Clock edge | x16 or x32 |
| 5 | M3 | Latch Enable | 0 | 0 | Random Read | x16 or x32 |
| | | | | 1 | Latch Enable Controlled Read | x16 or x32 |
| 4 to 2 | M2-M0 | Burst Length | XXX | 100 | 1 Word or Double-Word | x16 or x32 |
| | | | | 101 | 2 Words or Double-Words | x16 or x32 |
| | | | | 001 | 4 Words or Double-Words | x16 or x32 |
| | | | | 010 | 8 Words | x16 only |
| | | | | 111 | Continuous | x16 or x32 |
| | | | | Others | Reserved, Do Not Use. | |

Table 6. Burst Type Definition (x16 Bus Width)

| Burst Length | Starting Address (binary) | Sequential (decimal) | Interleaved (decimal) |
|--------------|------------------------------|-------------------------|--------------------------|
| | A3 A2 A1 | | |
| 2 | XX0 | 0, 1 | 0, 1 |
| | XX1 | 1, 0 | 1, 0 |
| 4 | X00 | 0, 1, 2, 3 | 0, 1, 2, 3 |
| | X01 | 1, 2, 3, 0 | 1, 0, 3, 2 |
| | X10 | 2, 3, 0, 1 | 2, 3, 0, 1 |
| | X11 | 3, 0, 1, 2 | 3, 2, 1, 0 |
| 8 | 000 | 0, 1, 2, 3, 4, 5, 6, 7 | 0, 1, 2, 3, 4, 5, 6, 7 |
| | 001 | 1, 2, 3, 4, 5, 6, 7, 0 | 1, 0, 3, 2, 5, 4, 7, 6 |
| | 010 | 2, 3, 4, 5, 6, 7, 0, 1 | 2, 3, 0, 1, 6, 7, 4, 5 |
| | 011 | 3, 4, 5, 6, 7, 0, 1, 2 | 3, 2, 1, 0, 7, 6, 5, 4 |
| | 100 | 4, 5, 6, 7, 0, 1, 2, 3 | 4, 5, 6, 7, 0, 1, 2, 3 |
| | 101 | 5, 6, 7, 0, 1, 2, 3, 4 | 5, 4, 7, 6, 1, 0, 3, 2 |
| | 110 | 6, 7, 0, 1, 2, 3, 4, 5 | 6, 7, 4, 5, 2, 3, 0, 1 |
| | 111 | 7, 0, 1, 2, 3, 4, 5, 6 | 7, 6, 5, 4, 3, 2, 1, 0 |
| Continuous | A | A, A+1, A+2... | Not Valid |

Note: X = 0 or 1.

Table 7. Burst Type Definition (x32 Bus Width)

| Burst Length | Starting Address (binary) | Sequential (decimal) | Interleaved (decimal) |
|--------------|------------------------------|-------------------------|--------------------------|
| | A3 A2 | | |
| 2 | X0 | 0, 1 | 0, 1 |
| | X1 | 1, 0 | 1, 0 |
| 4 | 00 | 0, 1, 2, 3 | 0, 1, 2, 3 |
| | 01 | 1, 2, 3, 0 | 1, 0, 3, 2 |
| | 10 | 2, 3, 0, 1 | 2, 3, 0, 1 |
| | 11 | 3, 0, 1, 2 | 3, 2, 1, 0 |
| 8 | Not Valid | | |
| Continuous | A | A, A+1, A+2... | Not Valid |

Note: X = 0 or 1.

Table 8. Burst Performance

| X-Latency | Y-Latency | Bus Width | Clock Frequency | Mode |
|-----------|-----------|-----------|-----------------|--------------------|
| 7 | 1 | x16, x32 | ≤ 33 MHz | continuous only |
| 8 | | | | continuous, length |
| 9 | | | | continuous only |
| 7 | 2 | | | continuous only |
| 8 | | | | continuous, length |
| 9 | | | | continuous only |
| 10 | 1 | x16 only | ≤ 50 MHz | continuous only |
| 11 | | | | continuous, length |
| 12 | | | | continuous only |
| 13 | | | | continuous, length |
| 10 | 2 | | | continuous only |
| 11 | | | | continuous, length |
| 12 | | | | continuous only |
| 13 | | | | continuous, length |
| 13 | 2(M9=0) | x16, x32 | ≤ 66 MHz | continuous only |
| 15 | | | | continuous, length |

COMMAND INTERFACE

All Bus Write operations to the memory are interpreted by the Command Interface. Commands consist of one or more sequential Bus Write operations. The Commands are summarized in Table 9, Commands. Refer to Table 9 in conjunction with the text descriptions below.

After Power-Up or a Reset operation the memory enters Read mode.

Synchronous Read operations and Latch Controlled Bus Read operations can only be used to read the memory array. The Electronic Signature, CFI or Status Register will be read in Asynchronous mode regardless of the Burst Control Register settings. Once the memory returns to Read Memory Array mode the bus will resume the setting in the Burst Configuration Register automatically.

Read Memory Array Command. The Read Memory Array command returns the memory to Read mode. One Bus Write cycle is required to issue the Read Memory Array command and return the memory to Read mode. Once the command is issued the memory remains in Read mode until another command is issued. From Read mode Bus Read operations will access the memory array.

While the Program/Erase Controller is executing a Program, Erase, Block Protect or Blocks Unprotect operation the memory will not accept the Read Memory Array command until the operation completes.

Read Electronic Signature Command. The Read Electronic Signature command is used to read the Manufacturer Code, the Device Code and the Block Protection Status. One Bus Write cycle is required to issue the Read Electronic Signature command. Once the command is issued subsequent Bus Read operations read the Manufacturer Code, the Device Code or the Block Protection Status until another command is issued; see Table 10, Read Electronic Signature.

Read Query Command. The Read Query Command is used to read data from the Common Flash Interface (CFI) Memory Area. One Bus Write cycle is required to issue the Read Query Command. Once the command is issued subsequent Bus Read operations read from the Common Flash Interface Memory Area. See Appendix B, Tables 29, 30, 31, 32, 33 and 34 for details on the information contained in the Common Flash Interface (CFI) memory area.

Note that the addresses for the Common Flash Interface Memory Area are A1-A23 for the M58LW128A and A2-A23 for the M58LW128B, regardless of the Bus Width selected.

Read Status Register Command. The Read Status Register command is used to read the Status

Register. One Bus Write cycle is required to issue the Read Status Register command. Once the command is issued subsequent Bus Read operations read the Status Register until another command is issued.

The Status Register information is present on the output data bus (DQ1-DQ7) when both Chip Enable and Output Enable are low, V_{IL} .

See the section on the Status Register and Table 12 for details on the definitions of the Status Register bits

Clear Status Register Command. The Clear Status Register command can be used to reset bits 1, 3, 4 and 5 in the Status Register to '0'. One Bus Write is required to issue the Clear Status Register command.

The bits in the Status Register are sticky and do not automatically return to '0' when a new Write to Buffer and Program, Erase, Block Protect or Block Unprotect command is issued. If any error occurs then it is essential to clear any error bits in the Status Register by issuing the Clear Status Register command before attempting a new Program, Erase or Resume command.

Block Erase Command. The Block Erase command can be used to erase a block. It sets all of the bits in the block to '1'. All previous data in the block is lost. If the block is protected then the Erase operation will abort, the data in the block will not be changed and the Status Register will output the error.

Two Bus Write operations are required to issue the command; the second Bus Write cycle latches the block address in the internal state machine and starts the Program/Erase Controller. Once the command is issued subsequent Bus Read operations read the Status Register. See the section on the Status Register for details on the definitions of the Status Register bits.

During the Erase operation the memory will only accept the Read Status Register command and the Program/Erase Suspend command. All other commands will be ignored. Typical Erase times are given in Table 11.

See Appendix C, Figure 27, Block Erase Flowchart and Pseudo Code, for a suggested flowchart on using the Block Erase command.

Write to Buffer and Program Command. The Write to Buffer and Program command is used to program the memory array.

Up to 2 pages of 8 Words (or 4 Double Words) can be loaded into the Write Buffer and programmed into the memory. The 2 pages are selected by address A4. Each Write Buffer has the same A5 -A23 addresses.

Four successive steps are required to issue the command.

1. One Bus Write operation is required to set up the Write to Buffer and Program Command. Issue the set up command with the selected memory Block Address where the program operation should occur (any address in the block where the values will be programmed can be used). Any Bus Read operations will start to output the Status Register after the 1st cycle.
2. Use one Bus Write operation to write the same block address along with the value N on the Data Inputs/Output, where N+1 is the number of Words (x16 Bus Width) or Double Words (x32 Bus Width) to be programmed.
3. Use N+1 Bus Write operations to load the address and data for each Word or Double Word into the Write Buffer. See the constraints on the address combinations listed below. The addresses must have the same A5-A23.
4. Finally, use one Bus Write operation to issue the final cycle to confirm the command and start the Program operation.

Invalid address combinations or failing to follow the correct sequence of Bus Write cycles will set an error in the Status Register and abort the operation without affecting the data in the memory array. The Status Register should be cleared before re-issuing the command.

The minimum buffer size for a program operation is an 8 Word (or 4 Double Word) page. Inside the page the 8 Words are selected by addresses A3, A2 and A1.

For any page, only one Write to Buffer and Program Command can be issued inside a previously erased block. Any further Program operations on that page must be preceded by an Erase operation on the respective block.

If the block being programmed is protected an error will be set in the Status Register and the operation will abort without affecting the data in the memory array. The block must be unprotected using the Blocks Unprotect command or by using the Blocks Temporary Unprotect feature of the Reset/Power-Down pin, \overline{RP} .

See Appendix C, Figure 25, Write to Buffer and Program Flowchart and Pseudo Code, for a suggested flowchart on using the Write to Buffer and Program command.

Program/Erase Suspend Command. The Program/Erase Suspend command is used to pause a Write to Buffer and Program or Erase operation. The command will only be accepted during a Program or an Erase operation. It can be issued at any time during an Erase operation but will only be accepted during a Write to Buffer and Program

command if the Program/Erase Controller is running.

One Bus Write cycle is required to issue the Program/Erase Suspend command and pause the Program/Erase Controller. Once the command is issued it is necessary to poll the Program/Erase Controller Status bit (bit 7) to find out when the Program/Erase Controller has paused; no other commands will be accepted until the Program/Erase Controller has paused. After the Program/Erase Controller has paused, the memory will continue to output the Status Register until another command is issued.

During the polling period between issuing the Program/Erase Suspend command and the Program/Erase Controller pausing it is possible for the operation to complete. Once the Program/Erase Controller Status bit (bit 7) indicates that the Program/Erase Controller is no longer active, the Program Suspend Status bit (bit 2) or the Erase Suspend Status bit (bit 6) can be used to determine if the operation has completed or is suspended. For timing on the delay between issuing the Program/Erase Suspend command and the Program/Erase Controller pausing see Table 11.

During Program/Erase Suspend the Read Memory Array, Read Status Register, Read Electronic Signature, Read Query and Program/Erase Resume commands will be accepted by the Command Interface. Additionally, if the suspended operation was Erase then the Write to Buffer and Program, and the Program Suspend commands will also be accepted. When a program operation is completed inside a Block Erase Suspend the Read Memory Array command must be issued to reset the device in Read mode, then the Erase Resume command can be issued to complete the whole sequence. Only the blocks not being erased may be read or programmed correctly.

See Appendix C, Figure 26, Program Suspend & Resume Flowchart and Pseudo Code, and Figure 28, Erase Suspend & Resume Flowchart and Pseudo Code, for suggested flowcharts on using the Program/Erase Suspend command.

Program/Erase Resume Command. The Program/Erase Resume command can be used to restart the Program/Erase Controller after a Program/Erase Suspend operation has paused it. One Bus Write cycle is required to issue the Program/Erase Resume command. Once the command is issued subsequent Bus Read operations read the Status Register.

Set Burst Configuration Register Command. The Set Burst Configuration Register command is used to write a new value to the Burst Configuration Control Register which defines the burst length, type, X and Y latencies, Synchronous/

Asynchronous Read mode and the valid Clock edge configuration.

Two Bus Write cycles are required to issue the Set Burst Configuration Register command. Once the command is issued the memory returns to Read mode as if a Read Memory Array command had been issued.

The value for the Burst Configuration Register is always presented on A2-A17, regardless of the bus width that is selected. M0 is on A2, M1 on A3, etc.; the other address bits are ignored.

Block Protect Command. The Block Protect command is used to protect a block and prevent Program or Erase operations from changing the data in it. Two Bus Write cycles are required to issue the Block Protect command; the second Bus Write cycle latches the block address in the internal state machine and starts the Program/Erase Controller. Once the command is issued subsequent Bus Read operations read the Status Register. See the section on the Status Register for details on the definitions of the Status Register bits.

During the Block Protect operation the memory will only accept the Read Status Register command. All other commands will be ignored. Typical Block Protection times are given in Table 11.

The Block Protection bits are non-volatile, once set they remain set through Reset and Power-Down/Power-Up. They are cleared by a Blocks Unprotect command or temporary disabled by raising the Reset/Power-Down pin to V_{HH} and holding it at that level throughout a Block Erase or Write to Buffer and Program command.

Blocks Unprotect Command. The Blocks Unprotect command is used to unprotect all of the blocks. Two Bus Write cycles are required to issue the Blocks Unprotect command; the second Bus Write cycle starts the Program/Erase Controller. Once the command is issued subsequent Bus Read operations read the Status Register. See the section on the Status Register for details on the definitions of the Status Register bits.

During the Block Unprotect operation the memory will only accept the Read Status Register command. All other commands will be ignored. Typical Block Protection times are given in Table 11.

Table 9. Commands

| Command | Cycles | Bus Write Operations | | | | | | | |
|----------------------------------|--------|----------------------|------|------|------|------------|------|-------|------|
| | | 1st | | 2nd | | Subsequent | | Final | |
| | | Addr | Data | Addr | Data | Addr | Data | Addr | Data |
| Read Memory Array | 1 | X | FFh | | | | | | |
| Read Electronic Signature | 1 | X | 90h | | | | | | |
| Read Query | 1 | X | 98h | | | | | | |
| Read Status Register | 1 | X | 70h | | | | | | |
| Clear Status Register | 1 | X | 50h | | | | | | |
| Block Erase | 2 | X | 20h | BA | D0h | | | | |
| Write to Buffer and Program | 4 + N | BA | E8h | BA | N | PA | PD | X | D0h |
| Program/Erase Suspend | 1 | X | B0h | | | | | | |
| Program/Erase Resume | 1 | X | D0h | | | | | | |
| Set Burst Configuration Register | 2 | BCR | 60h | BCR | 03h | | | | |
| Block Protect | 2 | BA | 60h | BA | 01h | | | | |
| Blocks Unprotect | 2 | X | 60h | X | D0h | | | | |

Note: X Don't Care; PA Program Address; PD Program Data; BA Any address in the Block; N+1 Number of Addresses to Program; BCR Burst Configuration Register value.

Table 10. Read Electronic Signature

| Code | Bus Width ⁽³⁾ | Address ⁽⁴⁾ | Data (DQ31-DQ0) ⁽²⁾ |
|-------------------------|--------------------------|-------------------------|--|
| Manufacturer Code | x16 | 000000h | 0020h |
| | x32 | | 00000020h |
| Device Code | x16 | 000001h | 8818h (M58LW128A) 8819h (M58LW128B) |
| | x32 | | 00008819h (M58LW128B) |
| Block Protection Status | x16 | SBA ⁽¹⁾ +02h | 0000h (Block Unprotected) 0001h (Block Protected) |
| | x32 | | 00000000h (Block Unprotected) 00000001h (Block Protected) |

- Note: 1. SBA is the Start Base Address of each block.
2. DQ31-DQ16 are available in the M58LW128B only.
3. x32 Bus Width is available in the M58LW128B only.
4. The address is presented on A22-A2 in x32 mode, and on A22-A1 in x16 mode.

Table 11. Program, Erase Times and Program Erase Endurance Cycles

| Parameters | M58LW128A/B | | | | Unit |
|----------------------------------|-------------|------|----------------------------------|-----|--------|
| | Min | Typ | Typical after 100k W/E Cycles | Max | |
| Block (1Mb) Erase | | 0.75 | 0.75 | 5 | s |
| Block Program | | 0.8 | 0.8 | | s |
| Program Write Buffer | | 192 | 192 | | μs |
| Program Suspend Latency Time | | 3 | | 10 | μs |
| Erase Suspend Latency Time | | 10 | | 30 | μs |
| Block Protect Time | | 192 | | | μs |
| Blocks Unprotect Time | | 0.75 | | | s |
| Program/Erase Cycles (per Block) | 100,000 | | | | cycles |
| Data Retention | 20 | | | | years |

Note: (T_A = 0 to 70°C; V_{DD} = 2.7V to 3.6V; V_{DDQ} = 1.8V)

STATUS REGISTER

The Status Register provides information on the current or previous Program, Erase, Block Protect or Blocks Unprotect operation. The various bits in the Status Register convey information and errors on the operation. They are output on DQ7-DQ0.

To read the Status Register the Read Status Register command can be issued. The Status Register is automatically read after Program, Erase, Block Protect, Blocks Unprotect and Program/Erase Resume commands. The Status Register can be read from any address.

The Status Register can only be read using Asynchronous Bus Read operations. Once the memory returns to Read Memory Array mode the bus will resume the setting in the Burst Configuration Register automatically.

The contents of the Status Register can be updated during an Erase or Program operation by toggling the Output Enable pin or by dis-activating (Chip Enable, V_{IH}) and then reactivating (Chip Enable and Output Enable, V_{IL}) the device.

During a Program, Block Erase, Block Protect or Block Unprotect operation only bit 7 is valid, all other bits are high impedance. Once the operation is complete bit 7 is High and all other Status register bits are valid.

Status Register bits 5, 4, 3 and 1 are associated with various error conditions and can only be reset with the Clear Status Register command. The Status Register bits are summarized in Table 12, Status Register Bits. Refer to Table 12 in conjunction with the following text descriptions.

Program/Erase Controller Status (Bit 7). The Program/Erase Controller Status bit indicates whether the Program/Erase Controller is active or inactive. When the Program/Erase Controller Status bit is Low, V_{OL} , the Program/Erase Controller is active and all other Status Register bits are High Impedance; when the bit is High, V_{OH} , the Program/Erase Controller is inactive.

The Program/Erase Controller Status is Low immediately after a Program/Erase Suspend command is issued until the Program/Erase Controller pauses. After the Program/Erase Controller pauses the bit is High.

During Program, Erase, Block Protect and Blocks Unprotect operations the Program/Erase Controller Status bit can be polled to find the end of the operation. The other bits in the Status Register should not be tested until the Program/Erase Controller completes the operation and the bit is High.

After the Program/Erase Controller completes its operation the Erase Status, Program Status and Block Protection Status bits should be tested for errors.

Erase Suspend Status (Bit 6). The Erase Suspend Status bit indicates that an Erase operation has been suspended and is waiting to be resumed. The Erase Suspend Status should only be considered valid when the Program/Erase Controller Status bit is High (Program/Erase Controller inactive); after a Program/Erase Suspend command is issued the memory may still complete the operation rather than entering the Suspend mode.

When the Erase Suspend Status bit is Low, V_{OL} , the Program/Erase Controller is active or has completed its operation; when the bit is High, V_{OH} , a Program/Erase Suspend command has been issued and the memory is waiting for a Program/Erase Resume command.

When a Program/Erase Resume command is issued the Erase Suspend Status bit returns Low.

Erase Status (Bit 5). The Erase Status bit can be used to identify if the memory has failed to verify that the block has erased correctly or that all blocks have been unprotect successfully. The Erase Status bit should be read once the Program/Erase Controller Status bit is High (Program/Erase Controller inactive).

When the Erase Status bit is Low, V_{OL} , the memory has successfully verified that the block has erased correctly or all blocks have been unprotect successfully. When the Erase Status bit is High, V_{OH} , the erase operation has failed. Depending on the cause of the failure other Status Register bits may also be set to High, V_{OH} .

- If only the Erase Status bit (bit 5) is set High, V_{OH} , then the Program/Erase Controller has applied the maximum number of pulses to the block and still failed to verify that the block has erased correctly or that all the blocks have been unprotect successfully.
- If the failure is due to an erase or blocks unprotect with V_{PP} low, V_{OL} , then V_{PP} Status bit (bit 3) is also set High, V_{OH} .
- If the failure is due to an erase on a protected block then Block Protection Status bit (bit 1) is also set High, V_{OH} .
- If the failure is due to a program or erase incorrect command sequence then Program Status bit (bit 4) is also set High, V_{OH} .

Once set High, the Erase Status bit can only be reset Low by a Clear Status Register command or a hardware reset. If set High it should be reset before a new Program or Erase command is issued, otherwise the new command will appear to fail.

Program Status (Bit 4). The Program Status bit is used to identify a Program or Block Protect failure. The Program Status bit should be read once

the Program/Erase Controller Status bit is High (Program/Erase Controller inactive).

When the Program Status bit is Low, V_{OL} , the memory has successfully verified that the Write Buffer has programmed correctly or the block is protected. When the Program Status bit is High, V_{OH} , the program or block protect operation has failed. Depending on the cause of the failure other Status Register bits may also be set to High, V_{OH} .

- If only the Program Status bit (bit 4) is set High, V_{OH} , then the Program/Erase Controller has applied the maximum number of pulses to the byte and still failed to verify that the Write Buffer has programmed correctly or that the Block is protected.
- If the failure is due to a program or block protect with V_{PP} low, V_{OL} , then V_{PP} Status bit (bit 3) is also set High, V_{OH} .
- If the failure is due to a program on a protected block then Block Protection Status bit (bit 1) is also set High, V_{OH} .
- If the failure is due to a program or erase incorrect command sequence then Erase Status bit (bit 5) is also set High, V_{OH} .

Once set High, the Program Status bit can only be reset Low by a Clear Status Register command or a hardware reset. If set High it should be reset before a new Program or Erase command is issued, otherwise the new command will appear to fail.

V_{PP} Status (Bit 3). The V_{PP} Status bit can be used to identify if a Program, Erase, Block Protection or Block Unprotection operation has been attempted when V_{PP} is Low, V_{IL} . The V_{PP} pin is only sampled at the beginning of a Program or Erase operation.

When the V_{PP} Status bit is Low, V_{OL} , no Program, Erase, Block Protection or Block Unprotection operations have been attempted with V_{PP} Low, V_{IL} , since the last Clear Status Register command, or hardware reset. When the V_{PP} Status bit is High, V_{OH} , a Program, Erase, Block Protection or Block Unprotection operation has been attempted with V_{PP} Low, V_{IL} .

Once set High, the V_{PP} Status bit can only be reset by a Clear Status Register command or a hardware reset. If set High it should be reset before a new Program, Erase, Block Protection or Block Unprotection command is issued, otherwise the new command will appear to fail.

Program Suspend Status (Bit 2). The Program Suspend Status bit indicates that a Program operation has been suspended and is waiting to be resumed. The Program Suspend Status should only be considered valid when the Program/Erase Controller Status bit is High (Program/Erase Controller inactive); after a Program/Erase Suspend command is issued the memory may still complete the operation rather than entering the Suspend mode.

When the Program Suspend Status bit is Low, V_{OL} , the Program/Erase Controller is active or has completed its operation; when the bit is High, V_{OH} , a Program/Erase Suspend command has been issued and the memory is waiting for a Program/Erase Resume command.

When a Program/Erase Resume command is issued the Program Suspend Status bit returns Low.

Block Protection Status (Bit 1). The Block Protection Status bit can be used to identify if a Program or Erase operation has tried to modify the contents of a protected block.

When the Block Protection Status bit is Low, V_{OL} , no Program or Erase operations have been attempted to protected blocks since the last Clear Status Register command or hardware reset; when the Block Protection Status bit is High, V_{OH} , a Program (Program Status bit 4 set High) or Erase (Erase Status bit 5 set High) operation has been attempted on a protected block.

Once set High, the Block Protection Status bit can only be reset Low by a Clear Status Register command or a hardware reset. If set High it should be reset before a new Program or Erase command is issued, otherwise the new command will appear to fail.

Reserved (Bit 0). Bit 0 of the Status Register is reserved. Its value should be masked.

Table 12. Status Register Bits

| Operation | Bit 7 | Bit 6 | Bit 5 | Bit 4 | Bit 3 | Bit 2 | Bit 1 | R \bar{B} |
|---|-------|------------------|-------|-------|-------|-------|-------|-----------------|
| Program/Erase Controller Active | '0' | Hi-Z | | | | | | V _{OL} |
| Write Buffer not ready | '0' | Hi-Z | | | | | | V _{OL} |
| Write Buffer ready | '1' | X ⁽¹⁾ | '0' | '0' | '0' | '0' | '0' | Hi-Z |
| Program suspended | '1' | X ⁽¹⁾ | '0' | '0' | '0' | '1' | '0' | Hi-Z |
| Program/Block Protect completed successfully | '1' | X ⁽¹⁾ | '0' | '0' | '0' | '0' | '0' | Hi-Z |
| Program/Block Protect failure due to incorrect command sequence | '1' | X ⁽¹⁾ | '1' | '1' | '0' | '0' | '0' | Hi-Z |
| Program/Block Protect failure due to V _{PP} Error | '1' | X ⁽¹⁾ | '0' | '1' | '1' | '0' | '0' | Hi-Z |
| Program failure due to Block Protection | '1' | X ⁽¹⁾ | '0' | '1' | '0' | '0' | '1' | Hi-Z |
| Program/Block Protect failure due cell failure or unerasable cell | '1' | X ⁽¹⁾ | '0' | '1' | '0' | '0' | '0' | Hi-Z |
| Erase suspended | '1' | '1' | '0' | '0' | '0' | '0' | '0' | Hi-Z |
| Erase/Blocks Unprotect completed successfully | '1' | '0' | '0' | '0' | '0' | '0' | '0' | Hi-Z |
| Erase/Blocks Unprotect failure due to incorrect command sequence | '1' | X | '1' | '1' | '0' | '0' | '0' | Hi-Z |
| Erase/Block Unprotect failure due to V _{PP} Error | '1' | '0' | '1' | '0' | '1' | '0' | '0' | Hi-Z |
| Erase failure due to Block Protection | '1' | '0' | '1' | '0' | '0' | '0' | '1' | Hi-Z |
| Erase/Blocks Unprotect failure due to failed cell(s) in block | '1' | '0' | '1' | '0' | '0' | '0' | '0' | Hi-Z |

Note: 1. For Program operations during Erase Suspend Bit 6 is '1', otherwise Bit 6 is '0'.

MAXIMUM RATING

Stressing the device above the ratings listed in Table 13, Absolute Maximum Ratings, may cause permanent damage to the device. These are stress ratings only and operation of the device at these or any other conditions above those indicated in the Operating sections of this specification is

not implied. Exposure to Absolute Maximum Rating conditions for extended periods may affect device reliability. Refer also to the STMicroelectronics SURE Program and other relevant quality documents.

Table 13. Absolute Maximum Ratings

| Symbol | Parameter | Value | | Unit |
|------------------------------------|--|-------|-----------------------|------|
| | | Min | Max | |
| T _{BIAS} | Temperature Under Bias | -40 | 125 | °C |
| T _{STG} | Storage Temperature | -55 | 150 | °C |
| T _{LEAD} | Maximum TLEAD Temperature during soldering | | t.b.a. | °C |
| V _{IO} | Input or Output Voltage | -0.6 | V _{DDQ} +0.6 | V |
| V _{DD} , V _{DDQ} | Supply Voltage | -0.6 | 5.0 | V |
| V _{HH} | \overline{RP} Hardware Block Unprotect Voltage | -0.6 | 10 ⁽¹⁾ | V |

Note: 1. Cumulative time at a high voltage level of 10V should not exceed 80 hours on \overline{RP} pin.

DC AND AC PARAMETERS

This section summarizes the operating and measurement conditions, and the DC and AC characteristics of the device. The parameters in the DC and AC characteristics Tables that follow, are derived from tests performed under the Measure-

ment Conditions summarized in Table 14, Operating and AC Measurement Conditions. Designers should check that the operating conditions in their circuit match the measurement conditions when relying on the quoted parameters.

Table 14. Operating and AC Measurement Conditions

| Parameter | M58LW128 | | Units | |
|---|----------------|----------|-------|----|
| | Min | Max | | |
| Supply Voltage (V_{DD}) M58LW128 | 2.7 | 3.6 | V | |
| Input/Output Supply Voltage (V_{DDQ}) | 1.8 | V_{DD} | V | |
| Ambient Temperature (T_A) | Grade 1 | 0 | 70 | °C |
| | Grade 6 | -40 | 85 | °C |
| Load Capacitance (C_L) | 30 | | pF | |
| Clock Rise and Fall Times | | 3 | ns | |
| Input Rise and Fall Times | | 4 | ns | |
| Input Pulses Voltages | 0 to V_{DDQ} | | V | |
| Input and Output Timing Ref. Voltages | 0.5 V_{DDQ} | | V | |

Figure 10. AC Measurement Input Output Waveform

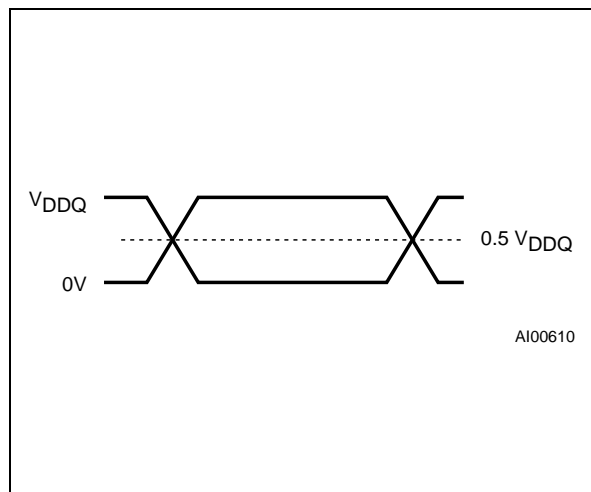


Figure 11. AC Measurement Load Circuit

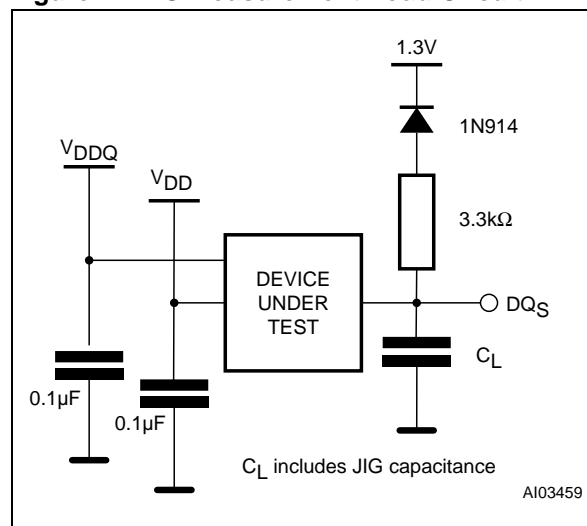


Table 15. Capacitance

| Symbol | Parameter | Test Condition | Typ | Max | Unit |
|-----------|--------------------|----------------|-----|-----|------|
| C_{IN} | Input Capacitance | $V_{IN} = 0V$ | 6 | 8 | pF |
| C_{OUT} | Output Capacitance | $V_{OUT} = 0V$ | 8 | 12 | pF |

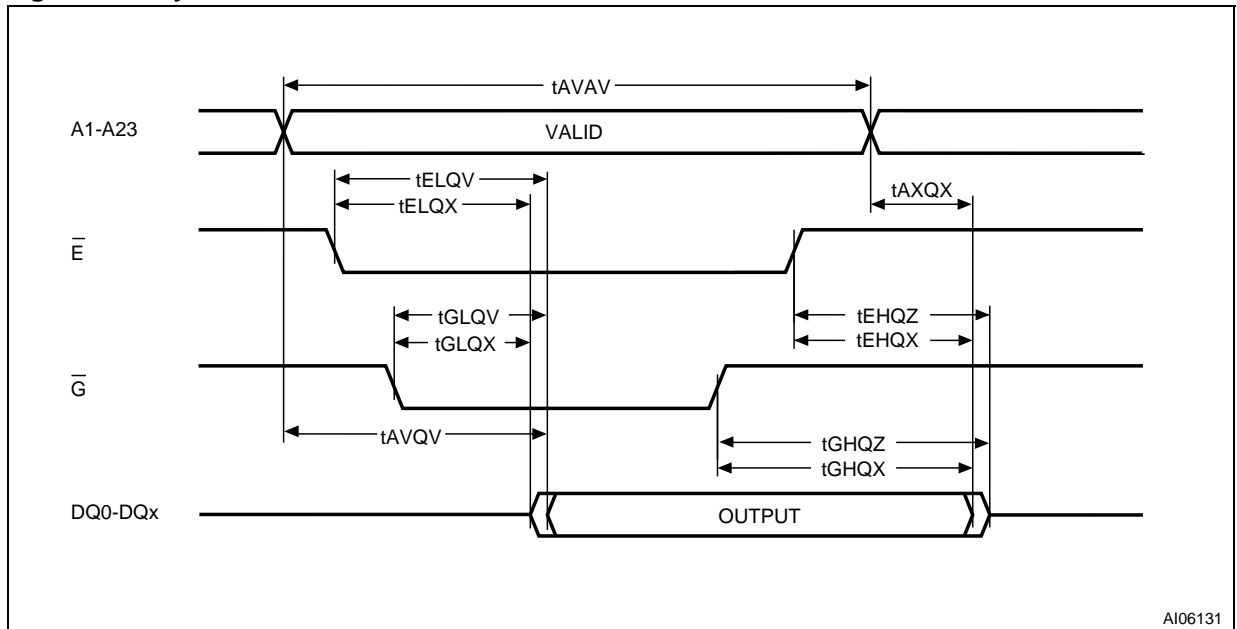
Note: 1. $T_A = 25^\circ\text{C}$, $f = 1\text{ MHz}$
 2. Sampled only, not 100% tested.

Table 16. DC Characteristics

| Symbol | Parameter | Test Condition | Min | Max | Unit |
|----------------|---|---|-----------------|-----------------|---------|
| I_{LI} | Input Leakage Current | $0V \leq V_{IN} \leq V_{DDQ}$ | | ± 1 | μA |
| I_{LO} | Output Leakage Current | $0V \leq V_{OUT} \leq V_{DDQ}$ | | ± 5 | μA |
| I_{DD} | Supply Current (Random Read) | $\bar{E} = V_{IL}, \bar{G} = V_{IH}, f_{add} = 6MHz$ | | 30 | mA |
| I_{DDB} | Supply Current (Burst Read) | $\bar{E} = V_{IL}, \bar{G} = V_{IH}, f_{clock} = 50MHz$ | | 50 | mA |
| I_{DD1} | Supply Current (Standby) | $\bar{E} = V_{IH}, \bar{RP} = V_{IH}$ | | 120 | μA |
| I_{DD2} | Supply Current (Reset/Power-Down) | $\bar{RP} = V_{IL}$ | | 120 | μA |
| I_{DD3} | Supply Current (Program or Erase, Set Protect Bit, Erase Protect Bit) | Program or Erase operation in progress | | 50 | mA |
| I_{DD4} | Supply Current (Erase/Program Suspend) | $\bar{E} = V_{IH}$ | | 50 | mA |
| V_{IL} | Input Low Voltage | | -0.5 | 0.8 | V |
| V_{IH} | Input High Voltage | | $V_{DDQ} - 0.8$ | $V_{DDQ} + 0.5$ | V |
| V_{OL} | Output Low Voltage | $I_{OL} = 100\mu A$ | | 0.1 | V |
| V_{OH} | Output High Voltage | $I_{OH} = -100\mu A$ | $V_{DDQ} - 0.1$ | | V |
| $V_{HH}^{(1)}$ | \bar{RP} Hardware Block Unprotect Voltage | Block Erase in progress, Write to Buffer and Program | 8.5 | 9.5 | V |
| I_{HH} | \bar{RP} Hardware Block Unprotect Current | $\bar{RP} = V_{HH}$ | | 1 | μA |
| V_{LKO} | V_{DD} Supply Voltage (Erase and Program lockout) | | | 2.2 | V |

Note: 1. Biasing \bar{RP} pin to V_{HH} is allowed for a maximum cumulative period of 80 hours.

Figure 12. Asynchronous Bus Read AC Waveforms



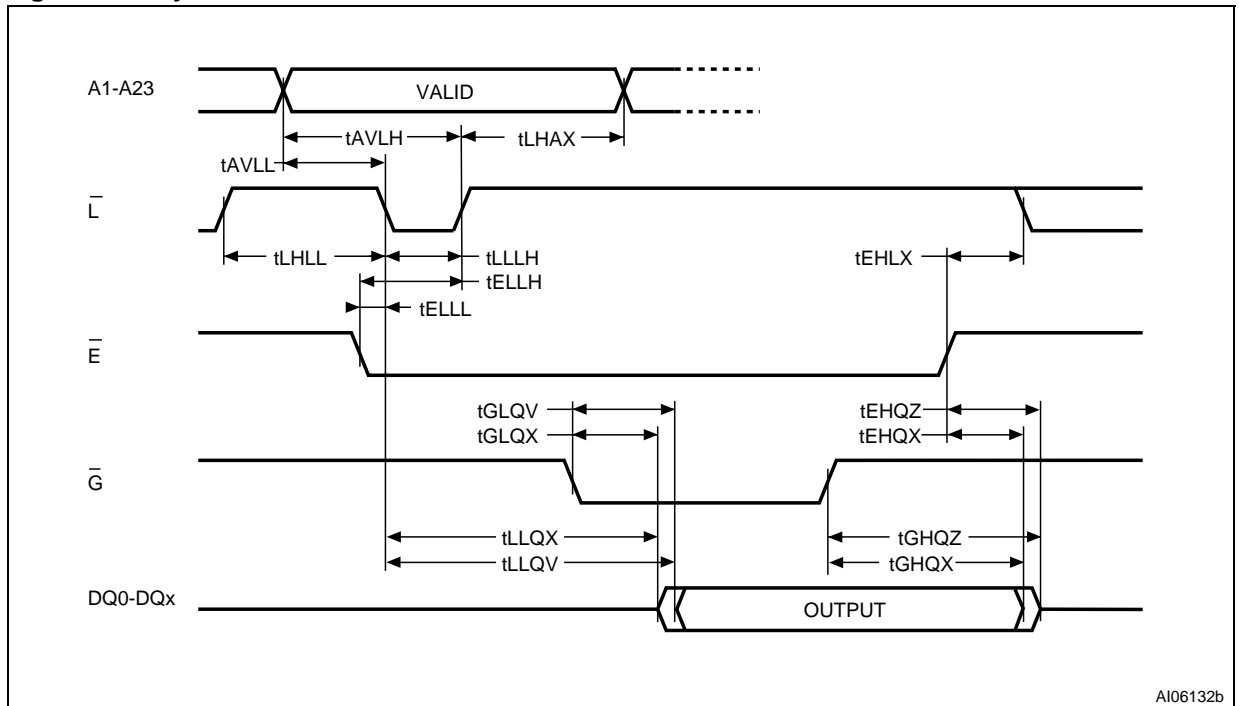
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Note: Asynchronous Read (M15 = 1), Random Read (M3 = 0)

Table 17. Asynchronous Bus Read AC Characteristics.

| Symbol | Parameter | Test Condition | | M58LW128 | Unit |
|------------|---|--------------------------------------|-----|----------|------|
| | | | | 150 | |
| t_{AVAV} | Address Valid to Address Valid | $\bar{E} = V_{IL}, \bar{G} = V_{IL}$ | Min | 150 | ns |
| t_{AVQV} | Address Valid to Output Valid | $\bar{E} = V_{IL}, \bar{G} = V_{IL}$ | Max | 150 | ns |
| t_{ELQX} | Chip Enable Low to Output Transition | $\bar{G} = V_{IL}$ | Min | 0 | ns |
| t_{ELQV} | Chip Enable Low to Output Valid | $\bar{G} = V_{IL}$ | Max | 150 | ns |
| t_{GLQX} | Output Enable Low to Output Transition | $\bar{E} = V_{IL}$ | Min | 0 | ns |
| t_{GLQV} | Output Enable Low to Output Valid | $\bar{E} = V_{IL}$ | Max | 30 | ns |
| t_{EHQX} | Chip Enable High to Output Transition | $\bar{G} = V_{IL}$ | Min | 0 | ns |
| t_{GHQX} | Output Enable High to Output Transition | $\bar{E} = V_{IL}$ | Min | 0 | ns |
| t_{AXQX} | Address Transition to Output Transition | $\bar{E} = V_{IL}, \bar{G} = V_{IL}$ | Min | 0 | ns |
| t_{EHQZ} | Chip Enable High to Output Hi-Z | $\bar{G} = V_{IL}$ | Max | 10 | ns |
| t_{GHQZ} | Output Enable High to Output Hi-Z | $\bar{E} = V_{IL}$ | Max | 10 | ns |

Figure 13. Asynchronous Latch Controlled Bus Read AC Waveforms



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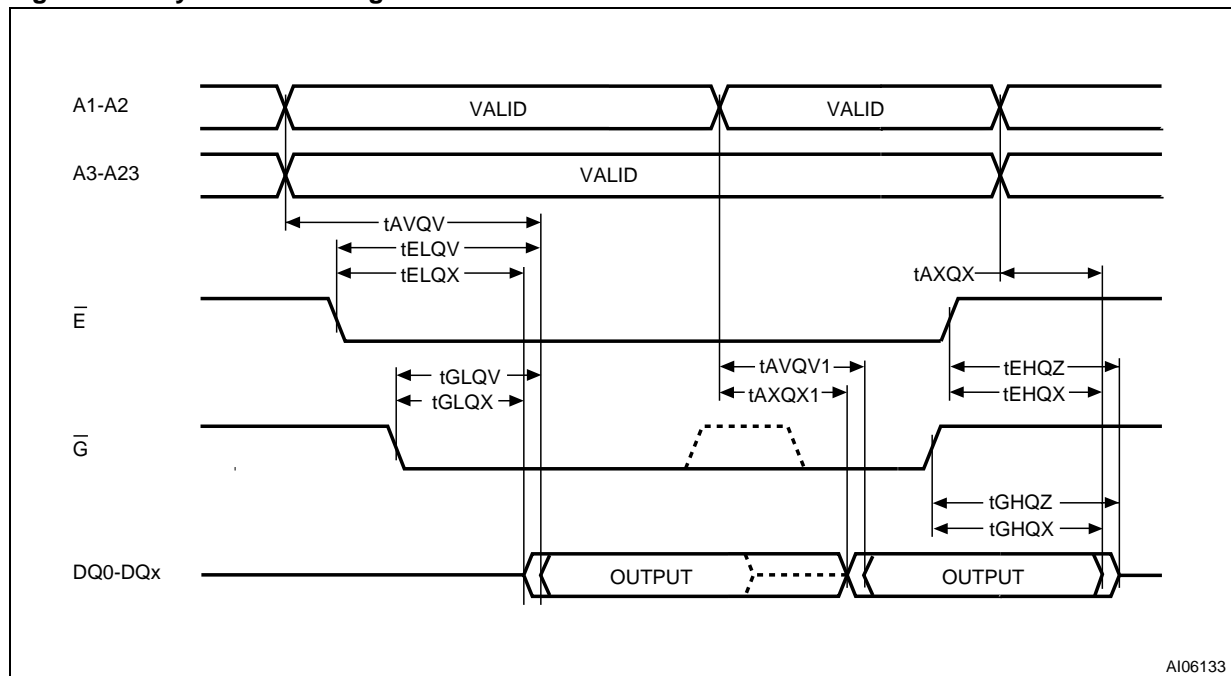
Note: Asynchronous Read (M15 = 1), Latch Enable Controlled (M3 = 1)

Table 18. Asynchronous Latch Controlled Bus Read AC Characteristics

| Symbol | Parameter | Test Condition | | M58LW128 | Unit |
|--------|---|--------------------------------------|-----|----------|------|
| | | | | 150 | |
| tAVLL | Address Valid to Latch Enable Low | $\bar{E} = V_{IL}$ | Min | 0 | ns |
| tAVLH | Address Valid to Latch Enable High | $\bar{E} = V_{IL}$ | Min | 10 | ns |
| tLHLL | Latch Enable High to Latch Enable Low | | Min | 10 | ns |
| tLLLH | Latch Enable Low to Latch Enable High | $\bar{E} = V_{IL}$ | Min | 10 | ns |
| tELL | Chip Enable Low to Latch Enable Low | | Min | 0 | ns |
| tELLH | Chip Enable Low to Latch Enable High | | Min | 10 | ns |
| tLLQX | Latch Enable Low to Output Transition | $\bar{E} = V_{IL}, \bar{G} = V_{IL}$ | Min | 0 | ns |
| tLLQV | Latch Enable Low to Output Valid | $\bar{E} = V_{IL}, \bar{G} = V_{IL}$ | Min | 150 | ns |
| tLHAX | Latch Enable High to Address Transition | $\bar{E} = V_{IL}$ | Min | 10 | ns |
| tGLQX | Output Enable Low to Output Transition | $\bar{E} = V_{IL}$ | Min | 0 | ns |
| tGLQV | Output Enable Low to Output Valid | $\bar{E} = V_{IL}$ | Max | 20 | ns |
| tEHLX | Chip Enable High to Latch Enable Transition | | Min | 0 | ns |

Note: For other timings see Table 17, Asynchronous Bus Read Characteristics.

Figure 14. Asynchronous Page Read AC Waveforms



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Note: Asynchronous Read (M15 = 1), Random (M3 = 0)

Table 19. Asynchronous Page Read AC Characteristics

| Symbol | Parameter | Test Condition | | M58LW128 | Unit |
|-------------|---|--------------------------------------|-----|----------|------|
| | | | | 150 | |
| t_{AXQX1} | Address Transition to Output Transition | $\bar{E} = V_{IL}, \bar{G} = V_{IL}$ | Min | 6 | ns |
| t_{AVQV1} | Address Valid to Output Valid | $\bar{E} = V_{IL}, \bar{G} = V_{IL}$ | Max | 25 | ns |

Note: For other timings see Table 17, Asynchronous Bus Read Characteristics.

Figure 15. Asynchronous Write AC Waveform, Write Enable Controlled

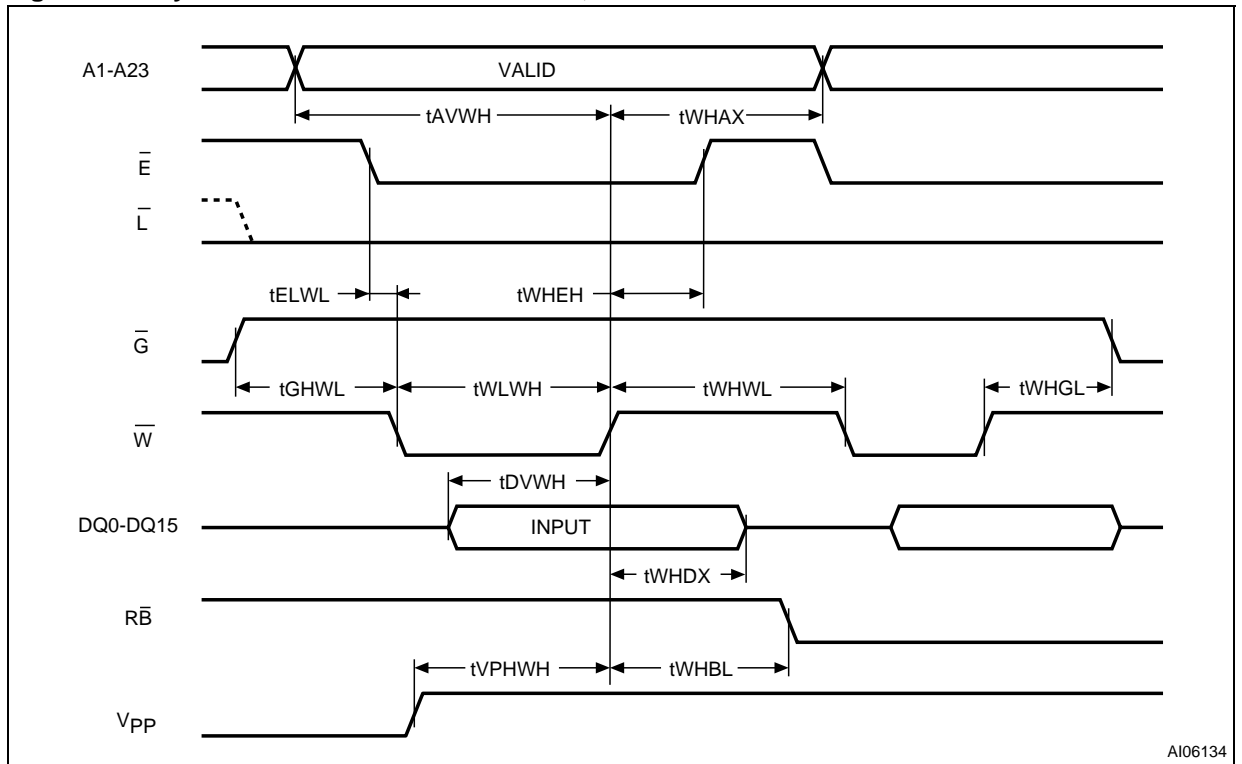


Figure 16. Asynchronous Latch Controlled Write AC Waveform, Write Enable Controlled

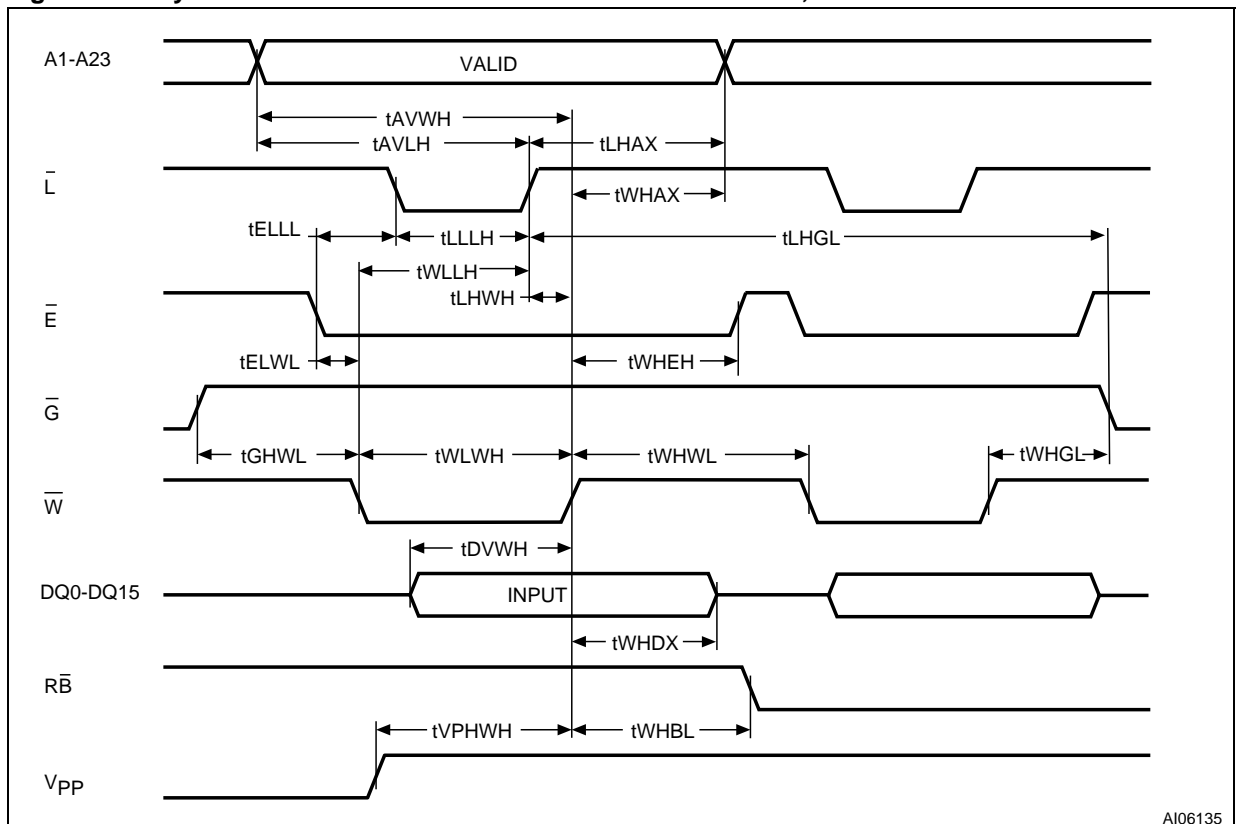
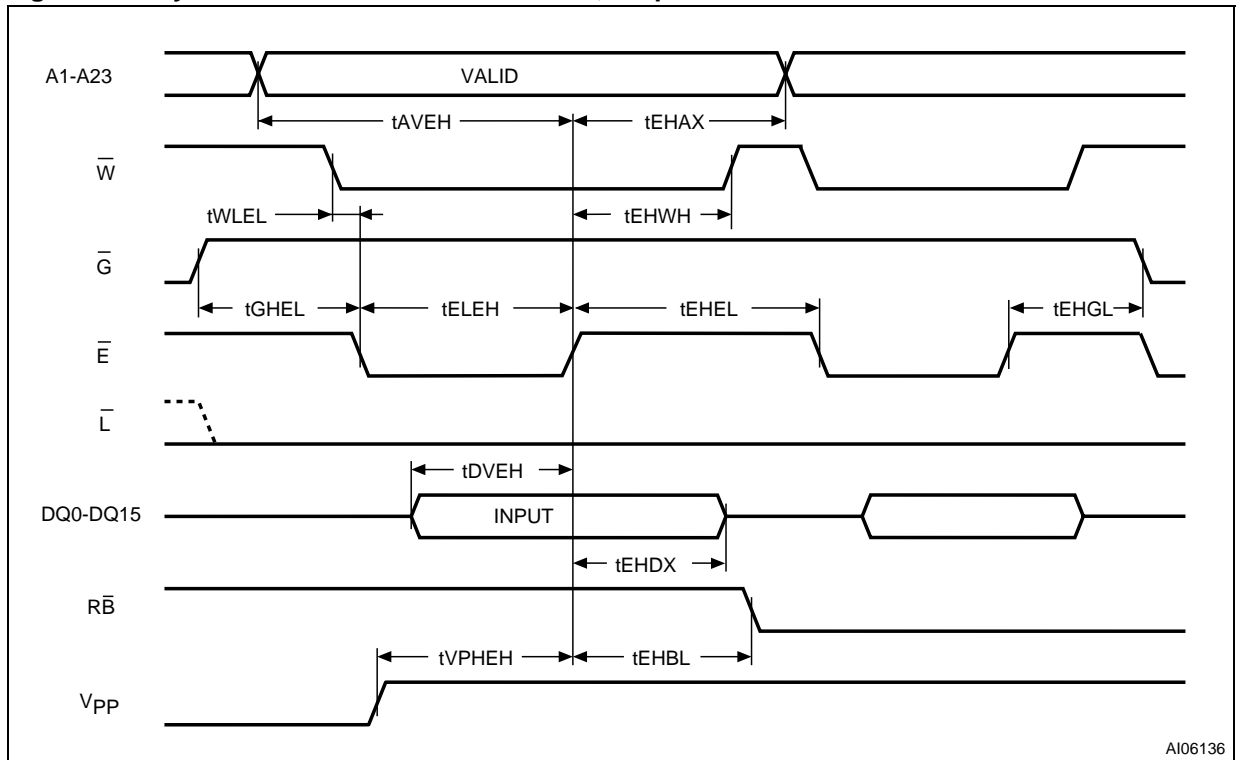


Table 20. Asynchronous Write and Latch Controlled Write AC Characteristics, Write Enable Controlled.

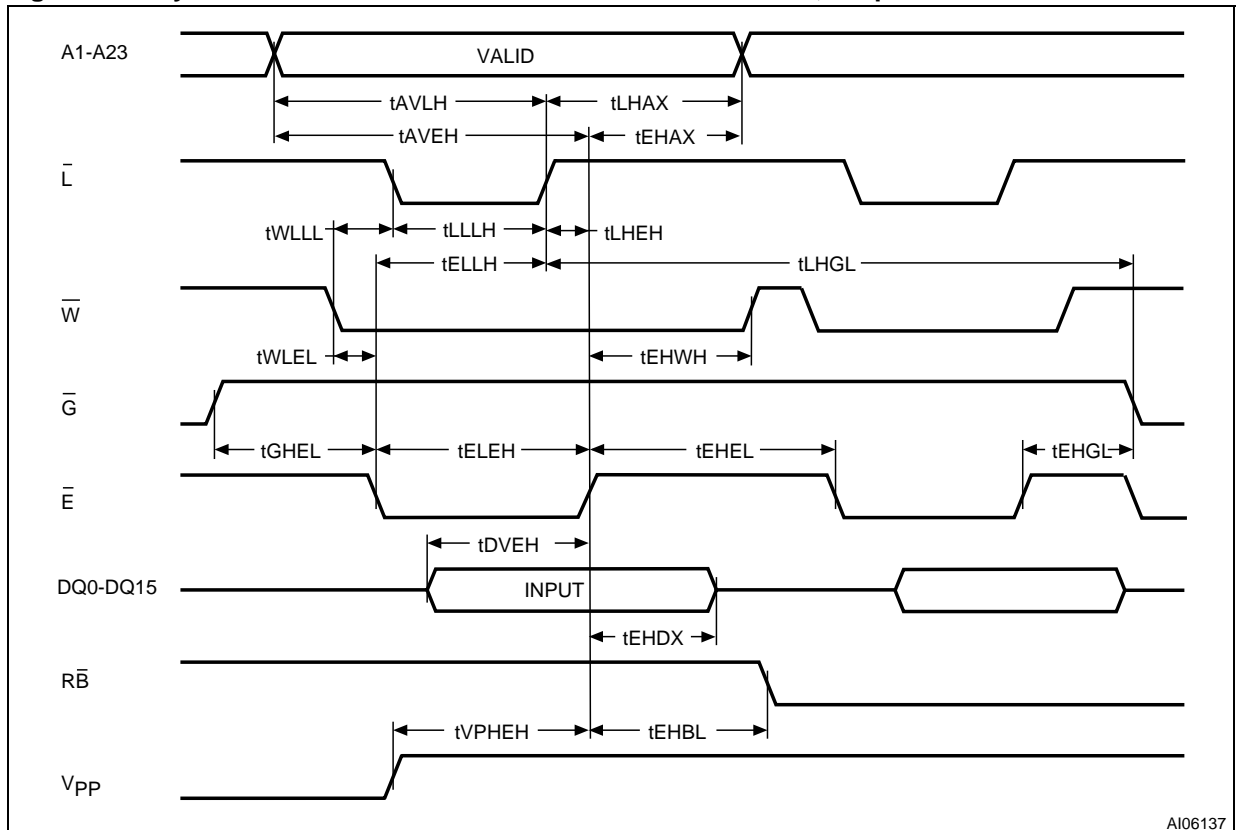
| Symbol | Parameter | Test Condition | | M58LW128 | Unit |
|--------------------|--|--------------------|-----|----------|------|
| | | | | 150 | |
| t _{AVLH} | Address Valid to Latch Enable High | | Min | 10 | ns |
| t _{AVWH} | Address Valid to Write Enable High | $\bar{E} = V_{IL}$ | Min | 50 | ns |
| t _{DVWH} | Data Input Valid to Write Enable High | $\bar{E} = V_{IL}$ | Min | 50 | ns |
| t _{ELWL} | Chip Enable Low to Write Enable Low | | Min | 0 | ns |
| t _{ELLL} | Chip Enable Low to Latch Enable Low | | Min | 0 | ns |
| t _{LHAX} | Latch Enable High to Address Transition | | Min | 3 | ns |
| t _{LHGL} | Latch Enable High to Output Enable Low | | Min | 35 | ns |
| t _{LHWH} | Latch Enable High to Write Enable High | | Min | 0 | ns |
| t _{LLLH} | Latch Enable low to Latch Enable High | | Min | 10 | ns |
| t _{LLWH} | Latch Enable Low to Write Enable High | | Min | 50 | ns |
| t _{VPHWH} | Program/Erase Enable High to Write Enable High | | Min | 0 | ns |
| t _{WHAX} | Write Enable High to Address Transition | $\bar{E} = V_{IL}$ | Min | 10 | ns |
| t _{WHBL} | Write Enable High to Ready/Busy low | | Max | 90 | ns |
| t _{WHDX} | Write Enable High to Input Transition | $\bar{E} = V_{IL}$ | Min | 0 | ns |
| t _{WHEH} | Write Enable High to Chip Enable High | | Min | 0 | ns |
| t _{GHWL} | Output Enable High to Write Enable Low | | Min | 20 | ns |
| t _{WHGL} | Write Enable High to Output Enable Low | | Min | 35 | ns |
| t _{WHWL} | Write Enable High to Write Enable Low | | Min | 30 | ns |
| t _{WLWH} | Write Enable Low to Write Enable High | $\bar{E} = V_{IL}$ | Min | 70 | ns |
| t _{WLLH} | Write Enable Low to Latch Enable High | $\bar{E} = V_{IL}$ | Min | 10 | ns |

Figure 17. Asynchronous Write AC Waveforms, Chip Enable Controlled



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Figure 18. Asynchronous Latch Controlled Write AC Waveforms, Chip Enable Controlled

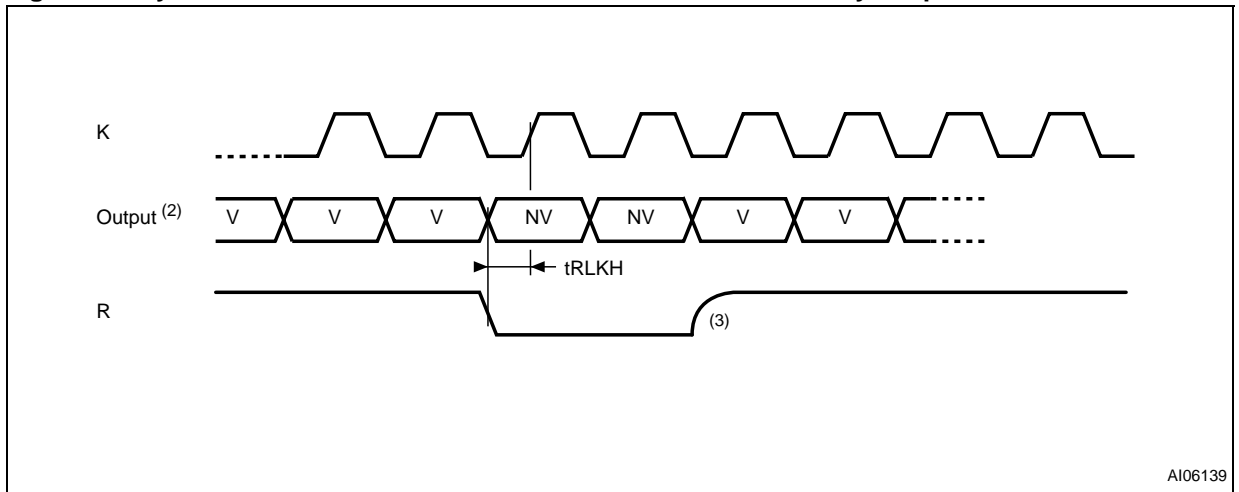


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Table 21. Asynchronous Write and Latch Controlled Write AC Characteristics, Chip Enable Controlled

| Symbol | Parameter | Test Condition | | M58LW128 | Unit |
|--------------------|---|-------------------------|-----|----------|------|
| | | | | 150 | |
| t _{AVLH} | Address Valid to Latch Enable High | | Min | 10 | ns |
| t _{AVEH} | Address Valid to Chip Enable High | $\overline{W} = V_{IL}$ | Min | 50 | ns |
| t _{DVEH} | Data Input Valid to Chip Enable High | $\overline{W} = V_{IL}$ | Min | 50 | ns |
| t _{WLEL} | Write Enable Low to Chip Enable Low | | Min | 0 | ns |
| t _{WLLL} | Write Enable Low to Latch Enable Low | | Min | 0 | ns |
| t _{LHAX} | Latch Enable High to Address Transition | | Min | 3 | ns |
| t _{LHGL} | Latch Enable High to Output Enable Low | | Min | 35 | ns |
| t _{LHEH} | Latch Enable High to Chip Enable High | | Min | 0 | ns |
| t _{LLLH} | Latch Enable low to Latch Enable High | | Min | 10 | ns |
| t _{LLEH} | Latch Enable Low to Chip Enable High | | Min | 50 | ns |
| t _{VPHEH} | Program/Erase Enable High to Chip Enable High | | Min | 0 | ns |
| t _{EHAX} | Chip Enable High to Address Transition | $\overline{W} = V_{IL}$ | Min | 10 | ns |
| t _{EHBL} | Chip Enable High to Ready/Busy low | | Max | 90 | ns |
| t _{EHDX} | Chip Enable High to Input Transition | $\overline{W} = V_{IL}$ | Min | 10 | ns |
| t _{EHWH} | Chip Enable High to Write Enable High | | Min | 0 | ns |
| t _{GHLEL} | Output Enable High to Chip Enable Low | | Min | 20 | ns |
| t _{EHGL} | Chip Enable High to Output Enable Low | | Min | 35 | ns |
| t _{EHLEL} | Chip Enable High to Chip Enable Low | | Min | 30 | ns |
| t _{ELEH} | Chip Enable Low to Chip Enable High | $\overline{W} = V_{IL}$ | Min | 70 | ns |
| t _{ELLH} | Chip Enable Low to Latch Enable High | $\overline{W} = V_{IL}$ | Min | 10 | ns |

Figure 20. Synchronous Burst Read - Continuous - Valid Data Ready Output



Note: 1. Valid Data Ready = Valid Low during valid clock edge ($M8 = 0$)

2. V= Valid output, NV= Not Valid output.

3. R is an open drain output. Depending on the Valid Data Ready pin capacitance load an external pull up resistor must be chosen according to the system clock period.

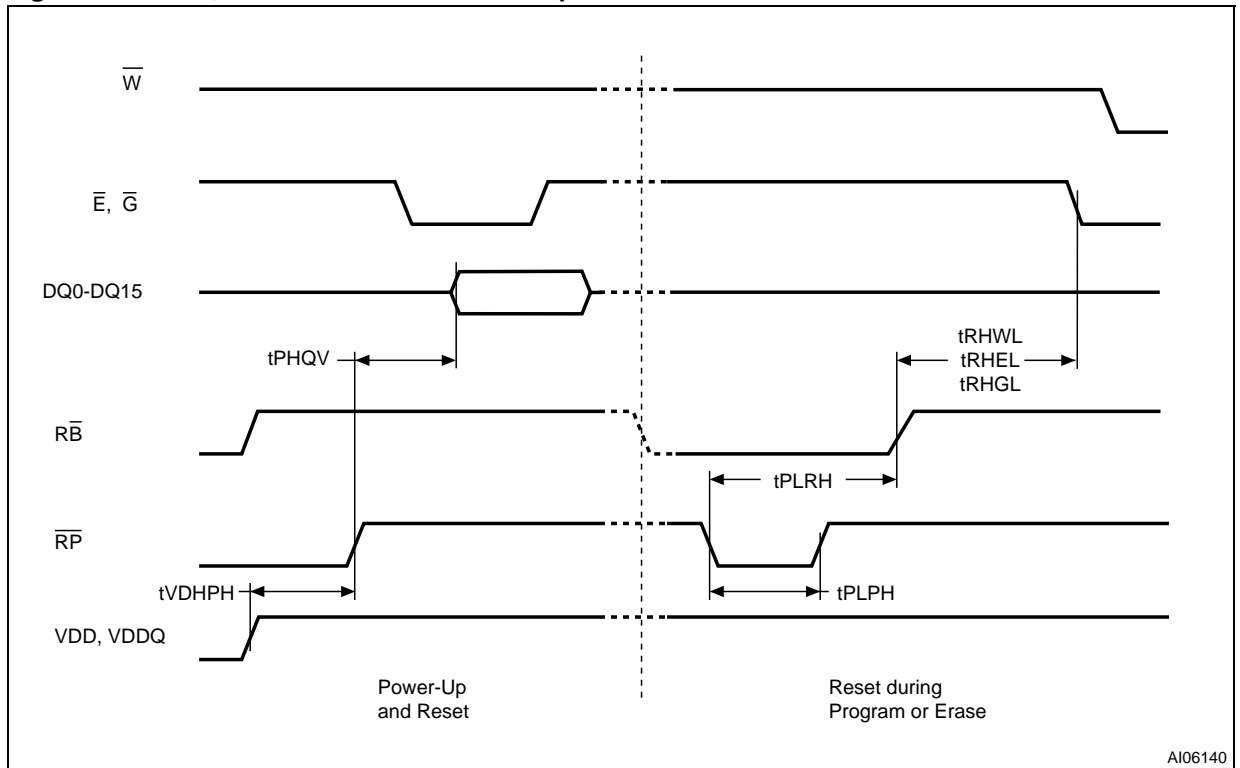
4. When the system clock frequency is between 33MHz and 50MHz and the Y latency is set to 2, values of \bar{B} sampled on odd clock cycles, starting from the first read are not considered.

Table 22. Synchronous Burst Read AC Characteristics

| Symbol | Parameter | Test Condition | | M58LW128 | Unit |
|-------------------|---|--|-----|----------|------|
| | | | | 150 | |
| t _{AVKH} | Address Valid to Active Clock Edge | $\bar{E} = V_{IL}$ | Min | 10 | ns |
| t _{AVLH} | Address Valid to Latch Enable High | $\bar{E} = V_{IL}$ | Min | 10 | ns |
| t _{BHKH} | Burst Address Advance High to Active Clock Edge | $\bar{E} = V_{IL}, \bar{G} = V_{IL}, \bar{L} = V_{IH}$ | Min | 10 | ns |
| t _{BLKH} | Burst Address Advance Low to Active Clock Edge | $\bar{E} = V_{IL}, \bar{G} = V_{IL}, \bar{L} = V_{IH}$ | Min | 10 | ns |
| t _{ELKH} | Chip Enable Low to Active Clock Edge | $\bar{E} = V_{IL}$ | Min | 10 | ns |
| t _{ELLH} | Chip Enable Low to Latch Enable High | $\bar{E} = V_{IL}$ | Min | 10 | ns |
| t _{GLKH} | Output Enable Low to Valid Clock Edge | $\bar{E} = V_{IL}, \bar{L} = V_{IH}$ | Min | 20 | ns |
| t _{KHAX} | Valid Clock Edge to Address Transition | $\bar{E} = V_{IL}$ | Min | 10 | ns |
| t _{KHLL} | Valid Clock Edge to Latch Enable Low | $\bar{E} = V_{IL}$ | Min | 0 | ns |
| t _{KHLH} | Valid Clock Edge to Latch Enable High | $\bar{E} = V_{IL}$ | Min | 0 | ns |
| t _{KHQX} | Valid Clock Edge to Output Transition | $\bar{E} = V_{IL}, \bar{G} = V_{IL}, \bar{L} = V_{IH}$ | Min | 3 | ns |
| t _{LLKH} | Latch Enable Low to Valid Clock Edge | $\bar{E} = V_{IL}$ | Min | 10 | ns |
| t _{LLLH} | Latch Enable Low to Latch Enable High | $\bar{E} = V_{IL}$ | Min | 10 | ns |
| t _{KHQV} | Valid Clock Edge to Output Valid | $\bar{E} = V_{IL}, \bar{G} = V_{IL}, \bar{L} = V_{IH}$ | Max | 20 | ns |
| t _{QVKH} | Output Valid to Active Clock Edge | $\bar{E} = V_{IL}, \bar{G} = V_{IL}, \bar{L} = V_{IH}$ | Min | 5 | ns |
| t _{RLKH} | Valid Data Ready Low to Valid Clock Edge | $\bar{E} = V_{IL}, \bar{G} = V_{IL}, \bar{L} = V_{IH}$ | Min | 5 | ns |
| t _{KHBL} | Active Clock Edge to Burst Address Advance Low | $\bar{E} = V_{IL}, \bar{G} = V_{IL}, \bar{L} = V_{IH}$ | Min | 0 | ns |
| t _{KHBH} | Active Clock Edge to Burst Address Advance High | $\bar{E} = V_{IL}, \bar{G} = V_{IL}, \bar{L} = V_{IH}$ | Min | 0 | ns |

Note: For other timings see Table 17, Asynchronous Bus Read Characteristics.

Figure 21. Reset, Power-Down and Power-Up AC Waveform



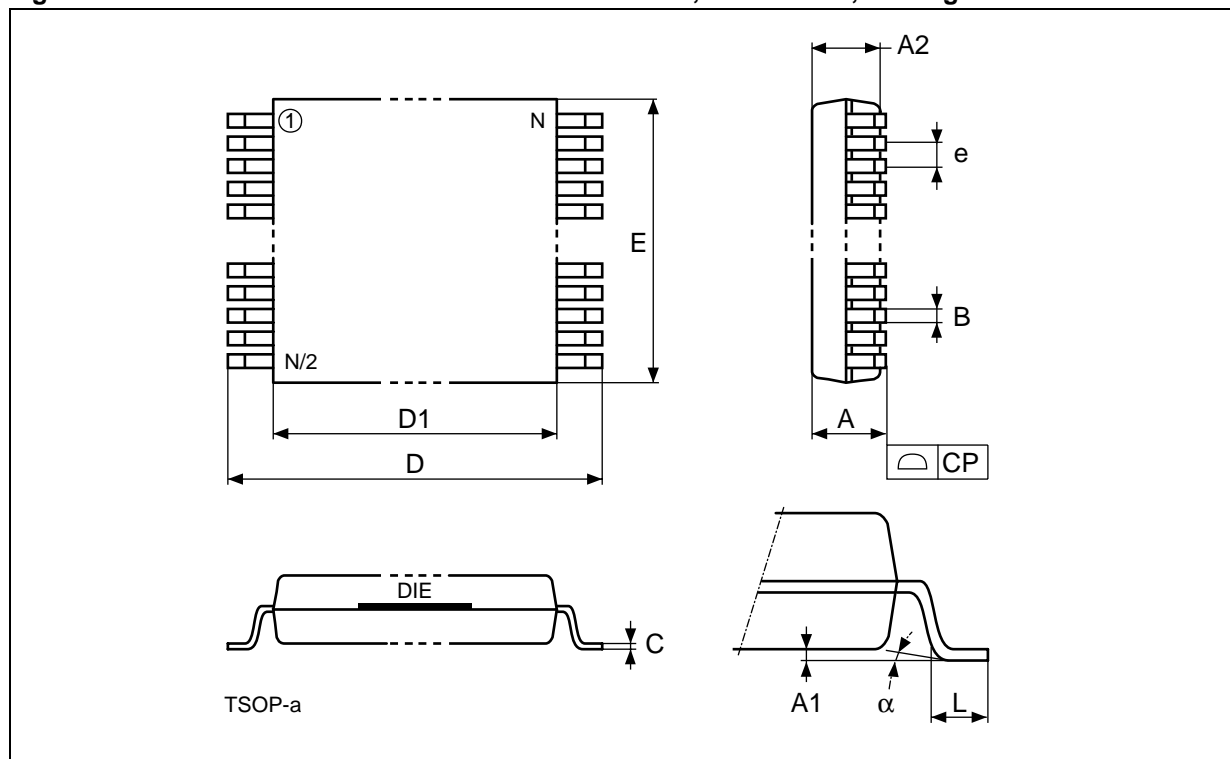
Note: Write Enable (\overline{W}) and Output Enable (\overline{G}) cannot be low together.

Table 23. Reset, Power-Down and Power-Up AC Characteristics

| Symbol | Parameter | | M58LW128 | Unit |
|--|--|-----|----------|---------|
| | | | 150 | |
| t_{PHQV} | Reset/Power-Down High to Data Valid | Min | 150 | ns |
| t_{RHWL} t_{RHEL} t_{RHGL} | Ready/Busy High to Write Enable Low, Chip Enable Low, Output Enable Low (Program/Erase Controller Active) | Min | 10 | μ s |
| t_{PLPH} | Reset/Power-Down Low to Reset/Power-Down High | Min | 100 | ns |
| t_{PLRH} | Reset/Power-Down Low to Ready High | Max | 30 | μ s |
| t_{VDHPH} | Supply Voltages High to Reset/Power-Down High | Min | 0 | μ s |

PACKAGE MECHANICAL

Figure 22. TSOP56 - 56 lead Plastic Thin Small Outline, 14 x 20 mm, Package Outline

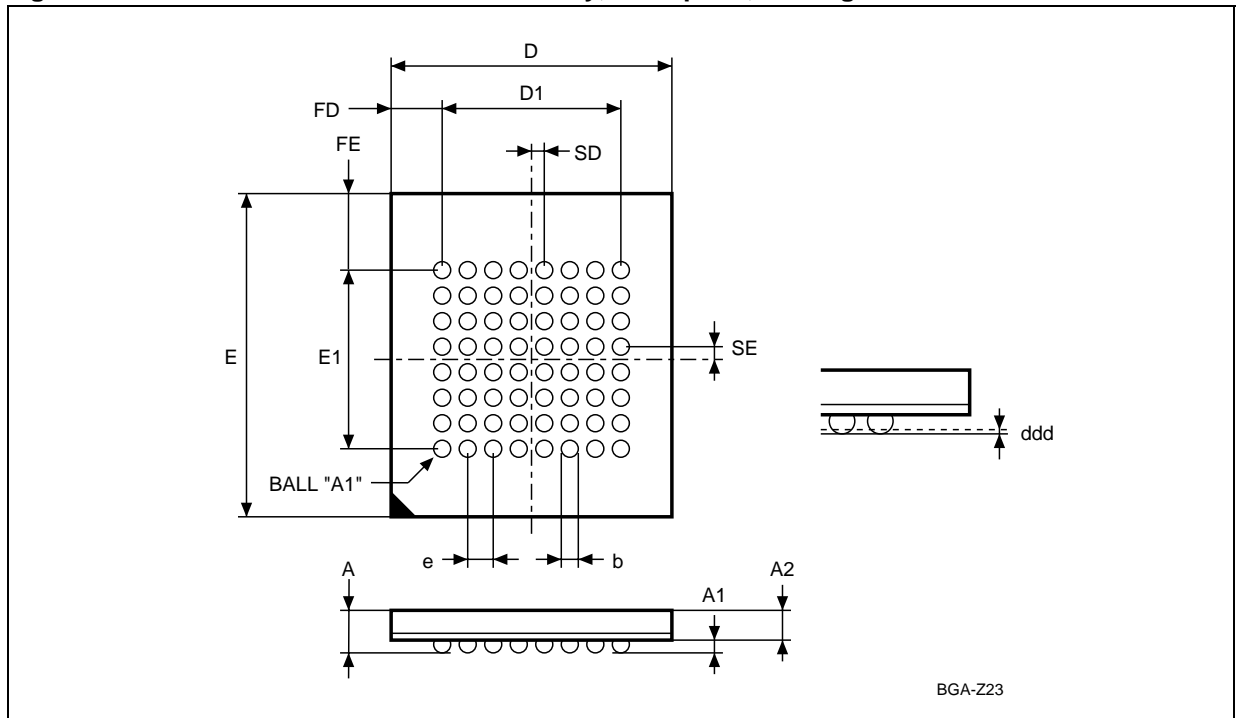


Note: Drawing is not to scale.

Table 24. TSOP56 - 56 lead Plastic Thin Small Outline, 14 x 20 mm, Package Mechanical Data

| Symbol | mm | | | inches | | |
|--------|------|-------|-------|--------|--------|--------|
| | Typ | Min | Max | Typ | Min | Max |
| A | | | 1.20 | | | 0.0472 |
| A1 | | 0.05 | 0.15 | | 0.0020 | 0.0059 |
| A2 | | 0.95 | 1.05 | | 0.0374 | 0.0413 |
| B | | 0.17 | 0.27 | | 0.0067 | 0.0106 |
| C | | 0.10 | 0.21 | | 0.0039 | 0.0083 |
| D | | 19.80 | 20.20 | | 0.7795 | 0.7953 |
| D1 | | 18.30 | 18.50 | | 0.7205 | 0.7283 |
| E | | 13.90 | 14.10 | | 0.5472 | 0.5551 |
| e | 0.50 | – | – | 0.0197 | – | – |
| L | | 0.50 | 0.70 | | 0.0197 | 0.0276 |
| α | | 0° | 5° | | 0° | 5° |
| N | 56 | | | 56 | | |
| CP | | | 0.10 | | | 0.0039 |

Figure 23. TBGA64 - 10x13mm - 8 x 8 ball array, 1mm pitch, Package Outline



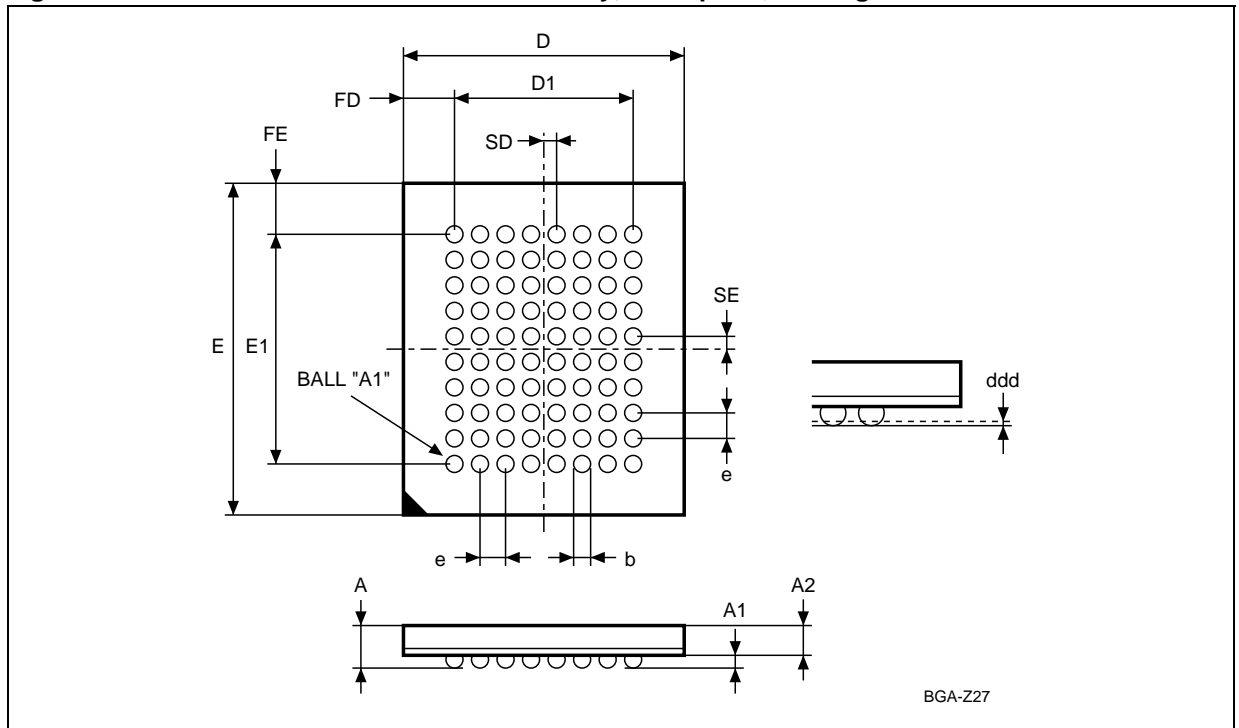
BGA-Z23

Note: Drawing is not to scale.

Table 25. TBGA64 - 10x13mm - 8 x 8 ball array, 1 mm pitch, Package Mechanical Data

| Symbol | millimeters | | | inches | | |
|--------|-------------|--------|--------|--------|--------|--------|
| | Typ | Min | Max | Typ | Min | Max |
| A | | | 1.200 | | | 0.0472 |
| A1 | 0.300 | 0.200 | 0.350 | 0.0118 | 0.0079 | 0.0138 |
| A2 | | | 0.850 | | | 0.0335 |
| b | | 0.400 | 0.500 | | 0.0157 | 0.0197 |
| D | 10.000 | 9.900 | 10.100 | 0.3937 | 0.3898 | 0.3976 |
| D1 | 7.000 | - | - | 0.2756 | - | - |
| ddd | | | 0.100 | | | 0.0039 |
| e | 1.000 | - | - | 0.0394 | - | - |
| E | 13.000 | 12.900 | 13.100 | 0.5118 | 0.5079 | 0.5157 |
| E1 | 7.000 | - | - | 0.2756 | - | - |
| FD | 1.500 | - | - | 0.0591 | - | - |
| FE | 3.000 | - | - | 0.1181 | - | - |
| SD | 0.500 | - | - | 0.0197 | - | - |
| SE | 0.500 | - | - | 0.0197 | - | - |

Figure 24. TBGA80 - 10x13mm - 8 x 10 ball array, 1mm pitch, Package Outline



Note: Drawing is not to scale.

Table 26. TBGA80 - 10x13mm - 8 x 10 ball array, 1mm pitch, Package Mechanical Data

| Symbol | millimeters | | | inches | | |
|--------|-------------|--------|--------|--------|--------|--------|
| | Typ | Min | Max | Typ | Min | Max |
| A | | | 1.200 | | | 0.0472 |
| A1 | 0.300 | 0.200 | 0.350 | 0.0118 | 0.0079 | 0.0138 |
| A2 | | | 0.850 | | | 0.0335 |
| b | | 0.400 | 0.500 | | 0.0157 | 0.0197 |
| D | 10.000 | 9.900 | 10.100 | 0.3937 | 0.3898 | 0.3976 |
| D1 | 7.000 | – | – | 0.2756 | – | – |
| ddd | | | 0.100 | | | 0.0039 |
| E | 13.000 | 12.900 | 13.100 | 0.5118 | 0.5079 | 0.5157 |
| E1 | 9.000 | – | – | 0.3543 | – | – |
| e | 1.000 | – | – | 0.0394 | – | – |
| FD | 1.500 | – | – | 0.0591 | – | – |
| FE | 2.000 | – | – | 0.0787 | – | – |
| SD | 0.500 | – | – | 0.0197 | – | – |
| SE | 0.500 | – | – | 0.0197 | – | – |

PART NUMBERING

Table 27. Ordering Information Scheme

| Example: | M58LW128A | 150 | N | 1 | T |
|--|-----------|-----|---|---|---|
| Device Type M58 | | | | | |
| Architecture L = Multi-Bit Cell, Burst Mode, Page Mode | | | | | |
| Operating Voltage W = $V_{DD} = 2.7V$ to $3.6V$; $V_{DDQ} = 1.8$ to V_{DD} | | | | | |
| Device Function 128A = 128 Mbit (x16), Uniform Block 128B = 128 Mbit (x16/x32), Uniform Block | | | | | |
| Speed 150 = 150 ns | | | | | |
| Package N = TSOP56: 14 x 20 mm (M58LW128A) ZA = TBGA64: 10x13mm, 1mm pitch (M58LW128A) ZA = TBGA80: 10x13mm, 1mm pitch (M58LW128B) | | | | | |
| Temperature Range 1 = 0 to 70 °C 6 = -40 to 85 °C | | | | | |
| Option T = Tape & Reel Packing E = Lead-free Package, Standard Packing F = Lead-free Package, Tape & Reel Packing | | | | | |

Note: Devices are shipped from the factory with the memory content bits erased to '1'.

For a list of available options (Speed, Package, etc...) or for further information on any aspect of this device, please contact the ST Sales Office nearest to you.

APPENDIX A. BLOCK ADDRESS TABLE

Table 28. Block Addresses

| Block Number | Address Range (x16 Bus Width) | Address Range (x32 Bus Width) |
|--------------|-------------------------------|-------------------------------|
| 128 | 7F0000h-7FFFFFFh | 3F8000h-3FFFFFFh |
| 127 | 7E0000h-7EFFFFh | 3F0000h-3F7FFFh |
| 126 | 7D0000h-7DFFFFh | 3E8000h-3EFFFFh |
| 125 | 7C0000h-7CFFFFh | 3E0000h-3E7FFFh |
| 124 | 7B0000h-7BFFFFh | 3D8000h-3DFFFFh |
| 123 | 7A0000h-7AFFFFh | 3D0000h-3D7FFFh |
| 122 | 790000h-79FFFFh | 3C8000h-3CFFFFh |
| 121 | 780000h-78FFFFh | 3C0000h-3C7FFFh |
| 120 | 770000h-77FFFFh | 3B8000h-3BFFFFh |
| 119 | 760000h-76FFFFh | 3B0000h-3B7FFFh |
| 118 | 750000h-75FFFFh | 3A8000h-3AFFFFh |
| 117 | 740000h-74FFFFh | 3A0000h-3A7FFFh |
| 116 | 730000h-73FFFFh | 398000h-39FFFFh |
| 115 | 720000h-72FFFFh | 390000h-397FFFh |
| 114 | 710000h-71FFFFh | 388000h-38FFFFh |
| 113 | 700000h-70FFFFh | 380000h-387FFFh |
| 112 | 6F0000h-6FFFFFFh | 378000h-37FFFFh |
| 111 | 6E0000h-6EFFFFh | 370000h-377FFFh |
| 110 | 6D0000h-6DFFFFh | 368000h-36FFFFh |
| 109 | 6C0000h-6CFFFFh | 360000h-367FFFh |
| 108 | 6B0000h-6BFFFFh | 358000h-35FFFFh |
| 107 | 6A0000h-6AFFFFh | 350000h-357FFFh |
| 106 | 690000h-69FFFFh | 348000h-34FFFFh |
| 105 | 680000h-68FFFFh | 340000h-347FFFh |
| 104 | 670000h-67FFFFh | 338000h-33FFFFh |
| 103 | 660000h-66FFFFh | 330000h-337FFFh |
| 102 | 650000h-65FFFFh | 328000h-32FFFFh |
| 101 | 640000h-64FFFFh | 320000h-327FFFh |
| 100 | 630000h-63FFFFh | 318000h-31FFFFh |
| 99 | 620000h-62FFFFh | 310000h-317FFFh |
| 98 | 610000h-61FFFFh | 308000h-30FFFFh |
| 97 | 600000h-60FFFFh | 300000h-307FFFh |
| 96 | 5F0000h-5FFFFFFh | 2F8000h-2FFFFFFh |

| Block Number | Address Range (x16 Bus Width) | Address Range (x32 Bus Width) |
|--------------|-------------------------------|-------------------------------|
| 95 | 5E0000h-5EFFFFh | 2F0000h-2F7FFFh |
| 94 | 5D0000h-5DFFFFh | 2E8000h-2EFFFFh |
| 93 | 5C0000h-5CFFFFh | 2E0000h-2E7FFFh |
| 92 | 5B0000h-5BFFFFh | 2D8000h-2DFFFFh |
| 91 | 5A0000h-5AFFFFh | 2D0000h-2D7FFFh |
| 90 | 590000h-59FFFFh | 2C8000h-2CFFFFh |
| 89 | 580000h-58FFFFh | 2C0000h-2C7FFFh |
| 88 | 570000h-57FFFFh | 2B8000h-2BFFFFh |
| 87 | 560000h-56FFFFh | 2B0000h-2B7FFFh |
| 86 | 550000h-55FFFFh | 2A8000h-2AFFFFh |
| 85 | 540000h-54FFFFh | 2A0000h-2A7FFFh |
| 84 | 530000h-53FFFFh | 298000h-29FFFFh |
| 83 | 520000h-52FFFFh | 290000h-297FFFh |
| 82 | 510000h-51FFFFh | 288000h-28FFFFh |
| 81 | 500000h-50FFFFh | 280000h-287FFFh |
| 80 | 4F0000h-4FFFFFFh | 278000h-27FFFFh |
| 79 | 4E0000h-4EFFFFh | 270000h-277FFFh |
| 78 | 4D0000h-4DFFFFh | 268000h-26FFFFh |
| 77 | 4C0000h-4CFFFFh | 260000h-267FFFh |
| 76 | 4B0000h-4BFFFFh | 258000h-25FFFFh |
| 75 | 4A0000h-4AFFFFh | 250000h-257FFFh |
| 74 | 490000h-49FFFFh | 248000h-24FFFFh |
| 73 | 480000h-48FFFFh | 240000h-247FFFh |
| 72 | 470000h-47FFFFh | 238000h-23FFFFh |
| 71 | 460000h-46FFFFh | 230000h-237FFFh |
| 70 | 450000h-45FFFFh | 228000h-22FFFFh |
| 69 | 440000h-44FFFFh | 220000h-227FFFh |
| 68 | 430000h-43FFFFh | 218000h-21FFFFh |
| 67 | 420000h-42FFFFh | 210000h-217FFFh |
| 66 | 410000h-41FFFFh | 208000h-20FFFFh |
| 65 | 400000h-40FFFFh | 200000h-207FFFh |
| 64 | 3F0000h-3FFFFFFh | 1F8000h-1FFFFFFh |
| 63 | 3E0000h-3EFFFFh | 1F0000h-1F7FFFh |
| 62 | 3D0000h-3DFFFFh | 1E8000h-1EFFFFh |



| Block Number | Address Range (x16 Bus Width) | Address Range (x32 Bus Width) |
|--------------|-------------------------------|-------------------------------|
| 61 | 3C0000h-3CFFFFh | 1E0000h-1E7FFFh |
| 60 | 3B0000h-3BFFFFh | 1D8000h-1DFFFFh |
| 59 | 3A0000h-3AFFFFh | 1D0000h-1D7FFFh |
| 58 | 390000h-39FFFFh | 1C8000h-1CFFFFh |
| 57 | 380000h-38FFFFh | 1C0000h-1C7FFFh |
| 56 | 370000h-37FFFFh | 1B8000h-1BFFFFh |
| 55 | 360000h-36FFFFh | 1B0000h-1B7FFFh |
| 54 | 350000h-35FFFFh | 1A8000h-1AFFFFh |
| 53 | 340000h-34FFFFh | 1A0000h-1A7FFFh |
| 52 | 330000h-33FFFFh | 198000h-19FFFFh |
| 51 | 320000h-32FFFFh | 190000h-197FFFh |
| 50 | 310000h-31FFFFh | 188000h-18FFFFh |
| 49 | 300000h-30FFFFh | 180000h-187FFFh |
| 48 | 2F0000h-2FFFFFh | 178000h-17FFFFh |
| 47 | 2E0000h-2EFFFFh | 170000h-177FFFh |
| 46 | 2D0000h-2DFFFFh | 168000h-16FFFFh |
| 45 | 2C0000h-2CFFFFh | 160000h-167FFFh |
| 44 | 2B0000h-2BFFFFh | 158000h-15FFFFh |
| 43 | 2A0000h-2AFFFFh | 150000h-157FFFh |
| 42 | 290000h-29FFFFh | 148000h-14FFFFh |
| 41 | 280000h-28FFFFh | 140000h-147FFFh |
| 40 | 270000h-27FFFFh | 138000h-13FFFFh |
| 39 | 260000h-26FFFFh | 130000h-137FFFh |
| 38 | 250000h-25FFFFh | 128000h-12FFFFh |
| 37 | 240000h-24FFFFh | 120000h-127FFFh |
| 36 | 230000h-23FFFFh | 118000h-11FFFFh |
| 35 | 220000h-22FFFFh | 110000h-117FFFh |
| 34 | 210000h-21FFFFh | 108000h-10FFFFh |
| 33 | 200000h-20FFFFh | 100000h-107FFFh |
| 32 | 1F0000h-1FFFFFh | 0F8000h-0FFFFFh |
| 31 | 1E0000h-1EFFFFh | 0F0000h-0F7FFFh |
| 30 | 1D0000h-1DFFFFh | 0E8000h-0EFFFFh |
| 29 | 1C0000h-1CFFFFh | 0E0000h-0E7FFFh |
| 28 | 1B0000h-1BFFFFh | 0D8000h-0DFFFFh |
| 27 | 1A0000h-1AFFFFh | 0D0000h-0D7FFFh |

| Block Number | Address Range (x16 Bus Width) | Address Range (x32 Bus Width) |
|--------------|-------------------------------|-------------------------------|
| 26 | 190000h-19FFFFh | 0C8000h-0CFFFFh |
| 25 | 180000h-18FFFFh | 0C0000h-0C7FFFh |
| 24 | 170000h-17FFFFh | 0B8000h-0BFFFFh |
| 23 | 160000h-16FFFFh | 0B0000h-0B7FFFh |
| 22 | 150000h-15FFFFh | 0A8000h-0AFFFFh |
| 21 | 140000h-14FFFFh | 0A0000h-0A7FFFh |
| 20 | 130000h-13FFFFh | 098000h-09FFFFh |
| 19 | 120000h-12FFFFh | 090000h-097FFFh |
| 18 | 110000h-11FFFFh | 088000h-08FFFFh |
| 17 | 100000h-10FFFFh | 080000h-087FFFh |
| 16 | 0F0000h-0FFFFFh | 078000h-07FFFFh |
| 15 | 0E0000h-0EFFFFh | 070000h-077FFFh |
| 14 | 0D0000h-0DFFFFh | 068000h-06FFFFh |
| 13 | 0C0000h-0CFFFFh | 060000h-067FFFh |
| 12 | 0B0000h-0BFFFFh | 058000h-05FFFFh |
| 11 | 0A0000h-0AFFFFh | 050000h-057FFFh |
| 10 | 090000h-09FFFFh | 048000h-04FFFFh |
| 9 | 080000h-08FFFFh | 040000h-047FFFh |
| 8 | 070000h-07FFFFh | 038000h-03FFFFh |
| 7 | 060000h-06FFFFh | 030000h-037FFFh |
| 6 | 050000h-05FFFFh | 028000h-02FFFFh |
| 5 | 040000h-04FFFFh | 020000h-027FFFh |
| 4 | 030000h-03FFFFh | 018000h-01FFFFh |
| 3 | 020000h-02FFFFh | 010000h-017FFFh |
| 2 | 010000h-01FFFFh | 008000h-00FFFFh |
| 1 | 000000h-00FFFFh | 000000h-007FFFh |

APPENDIX B. COMMON FLASH INTERFACE - CFI

The Common Flash Interface is a JEDEC approved, standardized data structure that can be read from the Flash memory device. It allows a system software to query the device to determine various electrical and timing parameters, density information and functions supported by the memory. The system can interface easily with the device, enabling the software to upgrade itself when necessary.

When the CFI Query Command (RCFI) is issued the device enters CFI Query mode and the data structure is read from the memory. Tables 29, 30,

31, 32, 33 and 34 show the addresses used to retrieve the data.

When the M58LW128B is used in x16 mode, A1 is the Least Significant Address. Toggling A1 will not change the CFI information available on the DQ15-DQ0 outputs.

To read the CFI, in the M58LW128A and M58LW128B devices, in x16 mode, addresses A23-A1 are used; for the x32 mode of the M58LW128B device only addresses A23-A2 are used. To read the CFI, in the M58LW128B device, in x16 mode, the address offsets shown must be multiplied by two in hexadecimal.

Table 29. Query Structure Overview

| Offset | Sub-section Name | Description |
|---------------------|---|---|
| 00h | | Manufacturer Code |
| 01h | | Device Code |
| 10h | CFI Query Identification String | Command set ID and algorithm data offset |
| 1Bh | System Interface Information | Device timing and voltage information |
| 27h | Device Geometry Definition | Flash memory layout |
| P(h) ⁽¹⁾ | Primary Algorithm-specific Extended Query Table | Additional information specific to the Primary Algorithm (optional) |
| A(h) ⁽²⁾ | Alternate Algorithm-specific Extended Query Table | Additional information specific to the Alternate Algorithm (optional) |
| (SBA+02)h | Block Status Register | Block-related Information |

Note: 1. Offset 0015h (x16) or 00000015h (x32) defines P which points to the Primary Algorithm Extended Query Address Table.
 2. Offset 0019h (x16) or 00000019h (x32) defines A which points to the Alternate Algorithm Extended Query Address Table.
 3. SBA is the Start Base Address for each block.

Table 30. CFI - Query Address and Data Output

| Address ⁽⁴⁾ A23-A1 (M58LW128A) A23-A2 (M58LW128B) | Data | | Instruction |
|--|--------------------------|----------|--|
| | DQ31-DQ16 ⁽⁶⁾ | DQ15-DQ0 | |
| 10h | 0000 | 0051h | Query ASCII String 0051h; "Q" 0052h; "R" 0059h; "Y" |
| 11h | 0000 | 0052h | |
| 12h | 0000 | 0059h | |
| 13h | 0000 | 0001h | Primary Vendor: Command Set and Control Interface ID Code |
| 14h | 0000 | 0000h | |
| 15h | 0000 | 0031h | Primary algorithm extended Query Address Table: P(h) |
| 16h | 0000 | 0000h | |
| 17h | 0000 | 0000h | Alternate Vendor: Command Set and Control Interface ID Code |
| 18h | 0000 | 0000h | |
| 19h | 0000 | 0000h | Alternate Algorithm Extended Query address Table |
| 1Ah ⁽⁵⁾ | 0000 | 0000h | |

Note: 1. The x8 or Byte Address mode is not available.

2. With the x16 Bus Width, the value of the address location of the CFI Query is independent of A1 pad (M58LW128B).

3. Query Data are always presented on DQ7-DQ0. DQ31-DQ8 are set to '0'.

4. For M58LW128B, A1 = Don't Care.

5. Offset 19h defines A which points to the Alternate Algorithm Extended Query Address Table.

6. DQ31-DQ16 are available in the M58LW128B only. They are in the high-impedance state when the device operates in x16 mode.

Table 31. CFI - Device Voltage and Timing Specification

| Address ⁽⁴⁾ A23-A1 (M58LW128A) A23-A2 (M58LW128B) | DQ31-DQ16 ⁽⁵⁾ | DQ15-DQ0 | Description |
|--|--------------------------|----------------------|---|
| 1Bh | 0000 | 0027h ⁽¹⁾ | V _{DD} Min, 2.7V |
| 1Ch | 0000 | 0036h ⁽¹⁾ | V _{DD} max, 3.6V |
| 1Dh | 0000 | 0000h ⁽²⁾ | V _{PP} min – Not Available |
| 1Eh | 0000 | 0000h ⁽²⁾ | V _{PP} max – Not Available |
| 1Fh | 0000 | 0000h ⁽³⁾ | 2 ⁿ μs typical time-out for Word Program – Not Available, DWord Program – Not Available |
| 20h | 0000 | 0008h | 2 ⁿ μs typical time-out for max Buffer Write |
| 21h | 0000 | 000Ah | 2 ⁿ ms, typical time-out for Erase Block |
| 22h | 0000 | 0000h ⁽³⁾ | 2 ⁿ ms, typical time-out for Chip Erase – Not Available |
| 23h | 0000 | 0000h ⁽³⁾ | 2 ⁿ x typical for Word Program time-out max – (Word and Dword Not Available) |
| 24h | 0000 | 0004h | 2 ⁿ x typical for Buffer Write time-out max |
| 25h | 0000 | 0004h | 2 ⁿ x typical for individual Block Erase time-out maximum |
| 26h | 0000 | 0000h ⁽³⁾ | 2 ⁿ x typical for Chip Erase max time-out – Not Available |

Note: 1. Bits are coded in Binary Code Decimal, bit7 to bit4 are scaled in Volts and bit3 to bit0 in mV.

2. Bit7 to bit4 are coded in Hexadecimal and scaled in Volts while bit3 to bit0 are in Binary Code Decimal and scaled in 100mV.

3. Not supported.

4. For M58LW128B, A1 = Don't Care.

5. DQ31-DQ16 are available in the M58LW128B only. They are in the high-impedance state when the device operates in x16 mode.

Table 32. Device Geometry Definition

| Address ⁽¹⁾ A23-A1 (M58LW128A) A23-A2 (M58LW128B) | DQ31-DQ16 ⁽²⁾ | DQ15-DQ0 | Description |
|--|--------------------------|----------|--|
| 27h | 0000 | 0018h | 2 ⁿ number of bytes memory Size |
| 28h | N/A | 0001h | Device Interface M58LW128A |
| | 0000 | 0004h | Device Interface M58LW128B |
| 29h | 0000 | 0000h | |
| 2Ah | 0000 | 0005h | Maximum number of bytes in Write Buffer, 2 ⁿ |
| 2Bh | 0000 | 0000h | |
| 2Ch | 0000 | 0001h | Bit7-0 = number of Erase Block Regions in device |
| 2Dh | 0000 | 007Fh | Number (n-1) of Erase Blocks of identical size; n=128 |
| 2Eh | 0000 | 0000h | |
| 2Fh | 0000 | 0000h | Erase Block Region Information x 256 bytes per Erase block (128K bytes) |
| 30h | 0000 | 0002h | |

Note: 1. For M58LW128B, A1 = Don't Care. N/A = Not Applicable.

2. DQ31-DQ16 are available in the M58LW128B only. They are in the high-impedance state when the device operates in x16 mode.

Table 33. Block Status Register

| Address A23-A1 (M58LW128A) A23-A2 (M58LW128B) | Data | | Selected Block Information |
|---|--------|---|------------------------------|
| (BA+2)h ⁽¹⁾ | bit0 | 0 | Block Unprotected |
| | | 1 | Block Protected |
| | bit7-1 | 0 | Reserved for future features |

Note: 1. BA specifies the block address location, A23-A17.

Table 34. Extended Query information

| Address offset | Address A23-A1 (M58LW128A) A23-A2 (M58LW128B) | DQ31-DQ16 ⁽¹⁾ | DQ15-DQ0 | Description |
|----------------|---|--------------------------|----------|---|
| (P)h | 31h | 0000h | 0050h | Query ASCII string - Extended Table 0050h; "P" 0052h; "R" 0049h; "I" |
| (P+1)h | 32h | 0000h | 0052h | |
| (P+2)h | 33h | 0000h | 0049h | |
| (P+3)h | 34h | 0000h | 0031h | Major version number |
| (P+4)h | 35h | 0000h | 0031h | Minor version number |
| (P+5)h | 36h | 0000h | 008Eh | Optional Feature: (1=yes, 0=no) bit0, Chip Erase Supported (0=no) |
| (P+6)h | 37h | 0000h | 0001h | bit1, Suspend Erase Supported (1=yes) |
| (P+7)h | 38h | 0000h | 0000h | bit2, Suspend Program Supported (1=yes) |
| (P+8)h | 39h | 0000h | 0000h | bit3, Protect/Unprotect Supported (1=yes) bit4, Queue Erase Supported (0=no) bit5, Instant individual block locking Supported (0=no) bit6, Protection Bits Supported (0=no) bit7, Page Read Supported (1=yes) bit8, Synchronous Read Supported (1=yes) Bit 31-9 reserved for future use |
| (P+9)h | 3Ah | 0000h | 0001h | Supported functions after Suspend: Program allowed after Erase Suspend (1=yes) (refer to Commands for other allowed functions) Bit 7-1 reserved for future use |
| (P+A)h | 3Bh | 0000h | 0001h | Block Status Register bit 0 Block Protect Bit Status active (1=yes) |
| (P+B)h | 3Ch | 0000h | 0000h | bits 1-15 are reserved |
| (P+C)h | 3Dh | 0000h | 0033h | V _{DD} OPTIMUM Program/Erase voltage conditions |
| (P+D)h | 3Eh | 0000h | 0033h | V _{PP} OPTIMUM Program/Erase voltage conditions |
| (P+E)h | 3Fh | 0000h | 0002h | OTP protection: 00 NA, 01 128-bit, 02 OTP area |
| (P+F)h | 40h | 0000h | 0004h | Page Read: 2 ⁿ Bytes (n = bits 0-7) |
| (P+10)h | 41h | 0000h | 0004h | Synchronous mode configuration fields |
| (P+11)h | 42h | 0000h | 0000h | n where 2 ⁿ⁺¹ is the number of Words/Double-Words for the burst Length (= 2) |
| (P+12)h | 43h | 0000h | 0001h | n where 2 ⁿ⁺¹ is the number of Words/Double-Words for the burst Length (= 4) |
| (P+13)h | 44h | 0000h | 0002h | n where 2 ⁿ⁺¹ is the number of Words/Double-Words for the burst Length (= 8) (x16 mode only) |
| (P+14)h | 45h | 0000h | 0007h | burst continuous |

Note: 1. DQ31-DQ16 are available in the M58LW128B only. They are in the high-impedance state when the device operates in x16 mode.

APPENDIX C. FLOW CHARTS

Figure 25. Write to Buffer and Program Flowchart and Pseudo Code

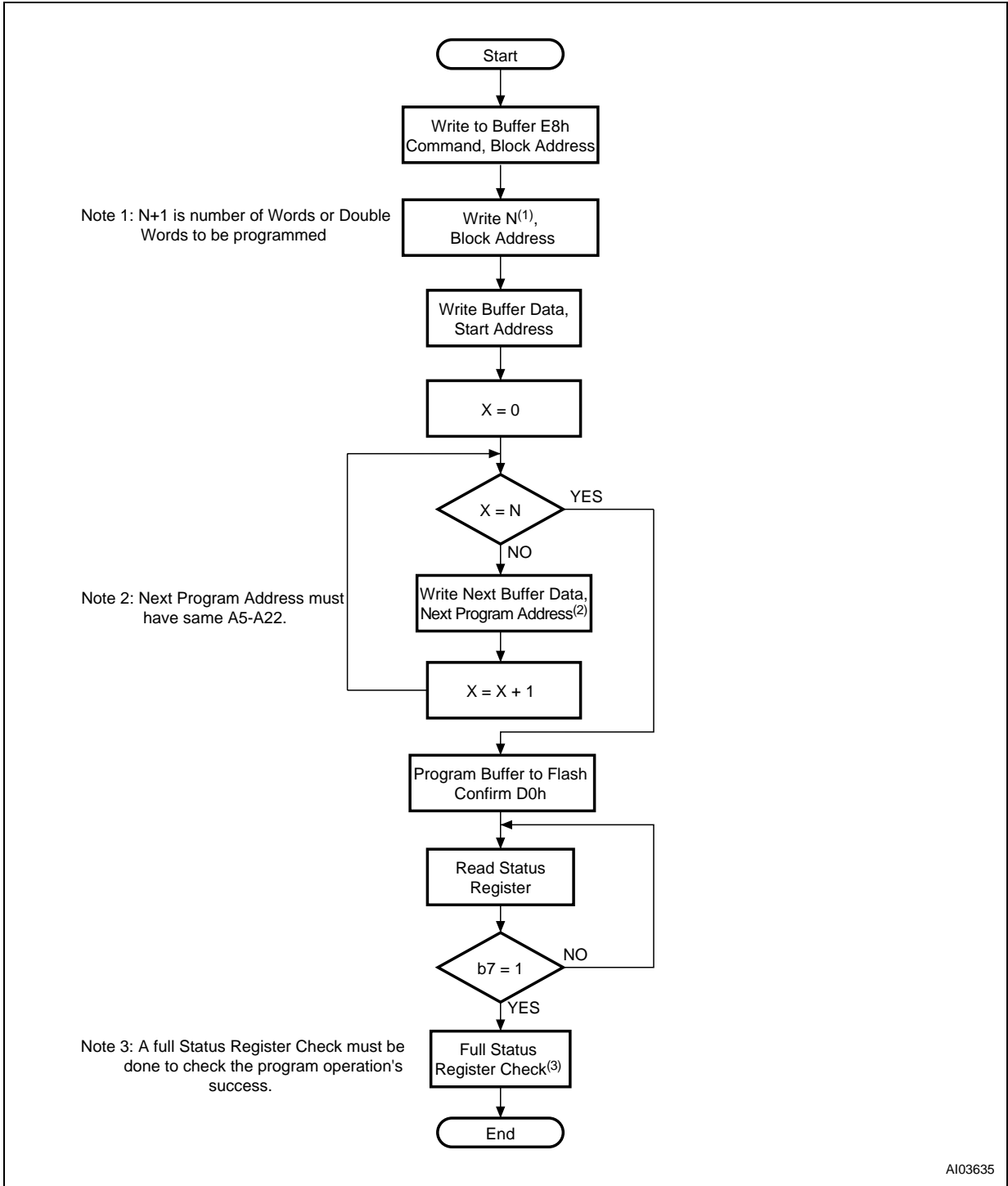
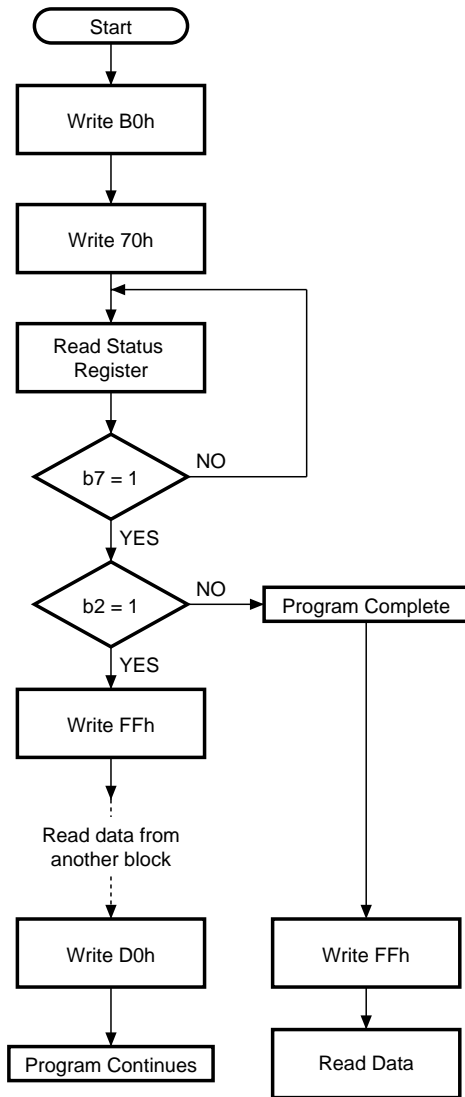


Figure 26. Program Suspend & Resume Flowchart and Pseudo Code



Program/Erase Suspend Command:

- write B0h
- write 70h

do:

- read status register

while b7 = 1

If b2 = 0, Program completed

Read Memory Array instruction:

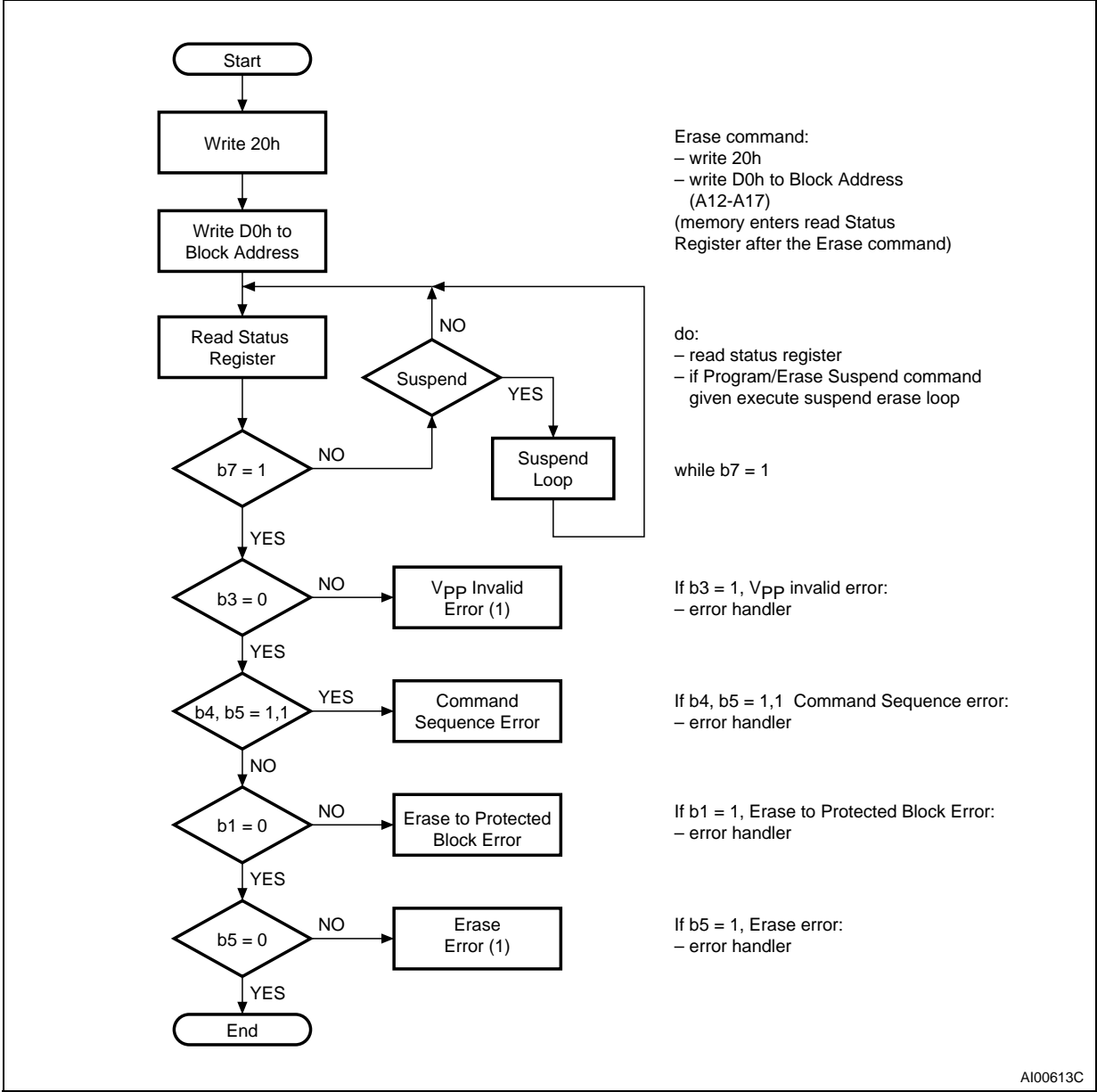
- write FFh
- one or more data reads from other blocks

Program Erase Resume Command:

- write D0h to resume erasure
- if the program operation completed then this is not necessary. The device returns to Read Array as normal (as if the Program/Erase Suspend command was not issued).

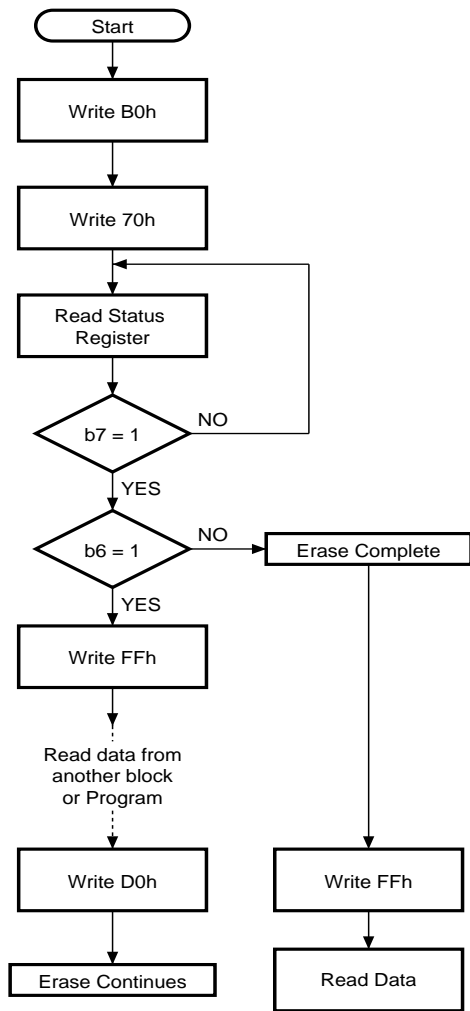
AI00612

Figure 27. Erase Flowchart and Pseudo Code



Note: 1. If an error is found, the Status Register must be cleared (Clear Status Register Command) before further Program or Erase operations.

Figure 28. Erase Suspend & Resume Flowchart and Pseudo Code



Program/Erase Suspend Command:

- write B0h
- write 70h

do:

- read status register

while b7 = 1

If b6 = 0, Erase completed

Read Memory Array command:

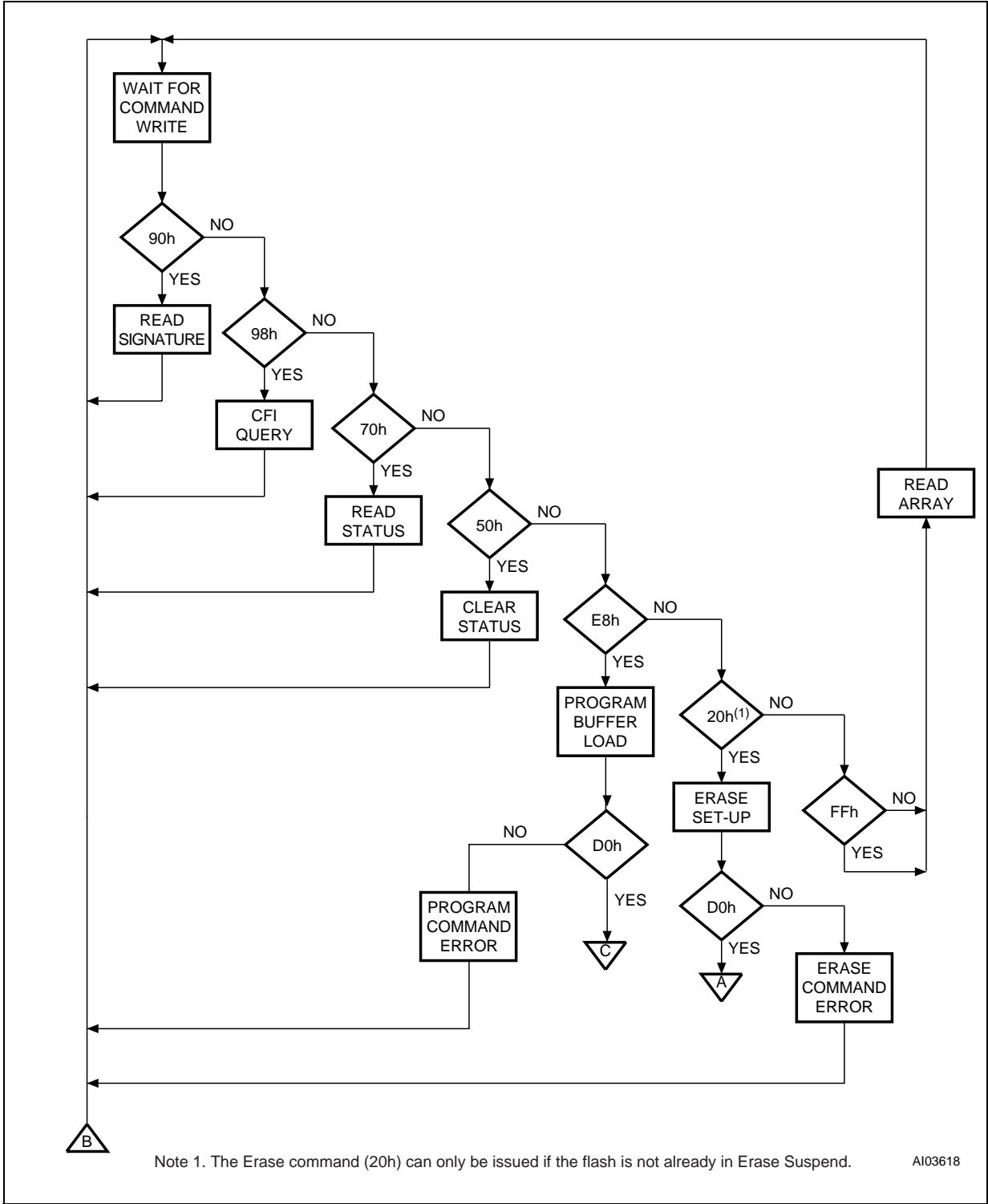
- write FFh
- one or more data reads from other blocks

Program/Erase Resume command:

- write D0h to resume the Erase operation
- if the Program operation completed then this is not necessary. The device returns to Read mode as normal (as if the Program/Erase suspend was not issued).

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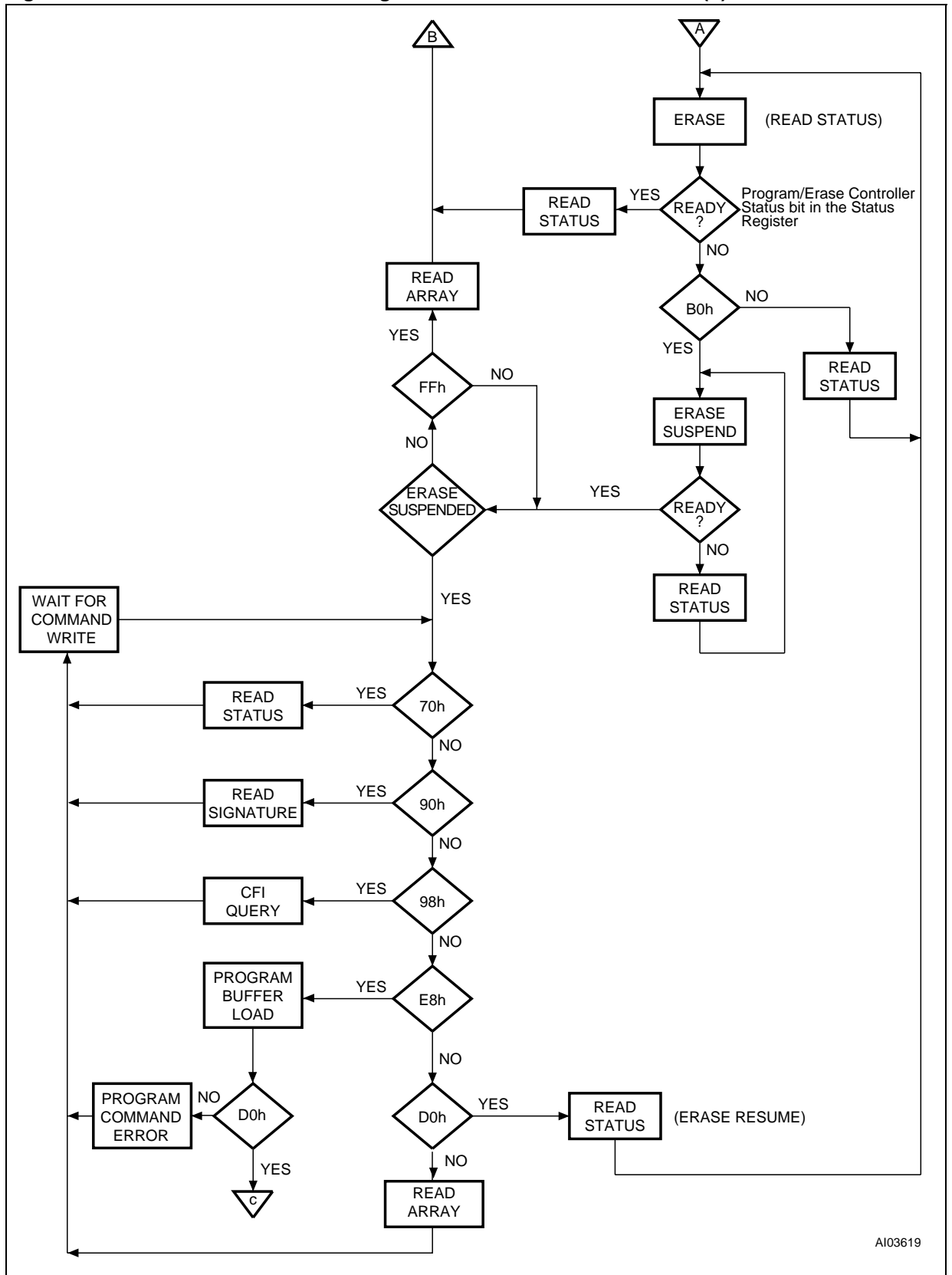
Figure 29. Command Interface and Program Erase Controller Flowchart (a)



Note 1. The Erase command (20h) can only be issued if the flash is not already in Erase Suspend.

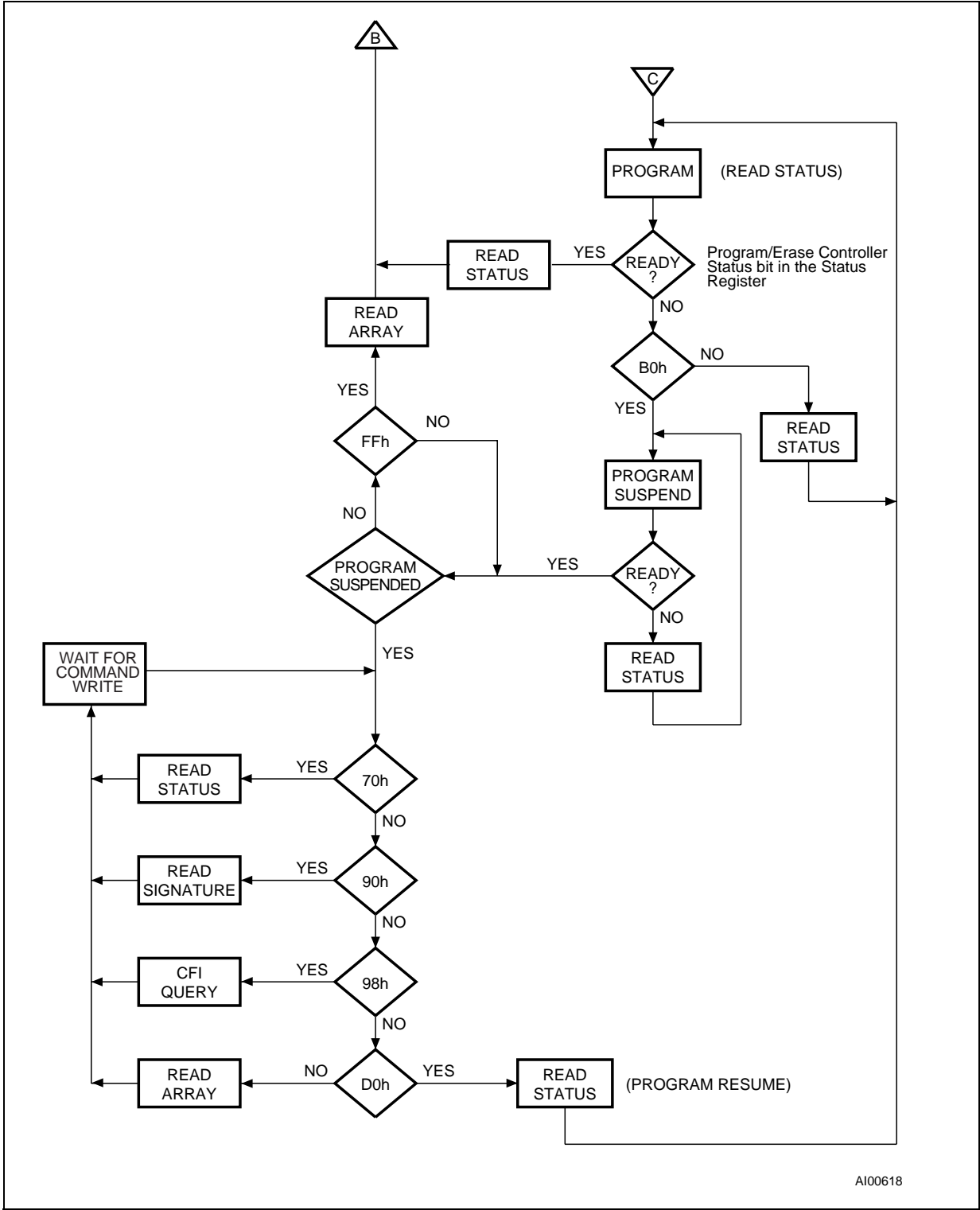
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Figure 30. Command Interface and Program Erase Controller Flowchart (b)



AI03619

Figure 31. Command Interface and Program Erase Controller Flowchart (c)



AI00618

REVISION HISTORY

Table 35. Document Revision History

| Date | Version | Revision Details |
|-------------|---------|--|
| 07-Dec-2001 | -01 | First Issue. |
| 16-Dec-2002 | 1.1 | Version number format modified (major.minor), Revision History moved to end of document. M58LW128A and M58LW128B device codes changed; Manufacturer code clarified. Table 10, Read Electronic Signature, clarified. Data Retention information added to Table 11, Program, Erase Times and Program Erase Endurance Cycles. CFI information (Table 30, Table 31, Table 32 and Table 34) clarified. Document Status changed to Preliminary Data. |
| 25-Feb-2003 | 1.2 | OTP size corrected. Word program not supported clarified in Table 31, CFI - Device Voltage and Timing Specification and DQ15-DQ0 values changed to 0000h for addresses 1Fh and 23h. Number (n-1) of Erase Blocks of identical size corrected in Table 32, Device Geometry Definition. ASCII for 0049h corrected in Table 34, Extended Query information. E and F lead-free packing options added to Table 27, Ordering Information Scheme. |

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